High Efficiency DC-DC Converter for EV Battery Charger Using Hybrid Resonant and PWM Technique

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ABSTRACT

The battery charger plays an important role in the development of electric vehicles (EVs) and plug-in hybrid electric vehicles (PHEVs). This thesis focuses on the DC-DC converter for high voltage battery charger and is divided into four chapters. The background related to EV battery charger is introduced, and the topologies of isolated DC-DC converter possibly applied in battery charge are sketched in Chapter 1. Since the EV battery charger is high voltage high power, the phase-shifted full bridge and LLC converters, which are popularly used in high power applications, are discussed in detail in Chapter 2. They are generally considered as high efficiency, high power density and high reliability, but their prominent features are also limited in certain range of operation. To make full use of the advantages and to avoid the limitation of the phase-shifted full bridge and LLC converters, a novel hybrid resonant and PWM converter combining resonant LLC half-bridge and phase shifted full-bridge topology is proposed and is described in Chapter 3. The converter achieves high efficiency and true soft switching for the entire operation range, which is very important for high voltage EV battery charger application. A 3.4 kW hardware prototype has been designed, implemented and tested to verify that the proposed hybrid converter truly avoids the disadvantages of LLC and phase-shifted full bridge converters while maintaining their advantages. In this proposed hybrid converter, the utilization efficiency of the auxiliary transformer is not that ideal. When the duty cycle is large, LLC converter charges one of the capacitors but the energy stored in the capacitor has no chance to be transferred to the output, resulting in the low utilization
efficiency of the auxiliary transformer. To utilize the auxiliary transformer fully while keeping all the prominent features of the previous hybrid converter in Chapter 3, an improved hybrid resonant and PWM converter is proposed in Chapter 4. The idea has been verified with simulations. The last chapter is the conclusion which summaries the key features and findings of the two proposed hybrid converters.
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CH1: Introduction

1.1 Background

As generally recognized, electric vehicles can achieve higher energy conversion efficiency, motor-regenerative braking capability, fewer local exhaust emissions, and less acoustic noise and vibration, as compared to gas-engine vehicles. The battery has an important role in the development of electric vehicles (EVs) and plug-in hybrid electric vehicles (PHEVs).

An EV shown in Fig.1.1 [1] is a vehicle propelled by electricity, unlike the conventional vehicles on road today which are major consumers of fossil fuels. This electricity can be either produced outside the vehicle and stored in a battery or produced on board with the help of fuel cells (FC’s). The development of EV’s started as early as 1834 when the first battery powered EV (tricycle) was built by Thomas Davenport [2], which appeared to be appalling, as it even preceded the invention of the ICE based on gasoline or diesel fuel. The development of EV’s was discontinued as they were not very convenient and efficient to use as they were very heavy and took a long time to recharge. Moreover, from the end of the year 1910, they also became more expensive than ICE.
vehicles. This led to the development of gasoline based vehicles. However, there are concerns over the depletion of fossil fuel and greenhouse gases causing long term global crisis like climatic changes and global warming. These concerns are shifting the focus back to development of automotive vehicles which use alternative fuels for operations. The development of such vehicles has become imperative not only for the scientists but also for the governments around the globe as can be substantiated by the Kyoto Protocol which has a total of 183 countries ratifying it (As on January 2009). The BEV has been since few years a very attractive research area both by car manufacturers and scientific researchers. The system architecture of HEV/EV is shown in Fig.1.2 [1].

![System architecture of HEV/EV](image-url)

**Fig.1.2 System architecture of HEV/EV**

**1.1.1 Typical Battery Charging Profile**

A battery is a device which converts chemical energy directly into electricity. It is an electrochemical galvanic cell or a combination of such cells which is capable of storing chemical energy. Batteries are more desirable for the use in vehicles, and particular traction batteries are most commonly used by EV manufacturers. Traction batteries include Lead Acid type, Nickel and Cadmium, Lithium ion/polymer, Sodium and Nickel Chloride, Nickel and Zinc. Batteries are expected to meet certain criteria in terms of energy density, power density, safety, and cycle life in order to be feasible for use in EVs and PHEVs. For this reason, the United States Advanced Battery Consortium (USABC) and Electrochemical Energy Storage Tech Team (EESTT) collaborated in 2006 to develop PHEV end of life battery requirements [3]. The battery for EVs should ideally provide a
high autonomy (i.e. the distance covered by the vehicle for one complete discharge of the battery starting from its potential) to the vehicle and have a high specific energy and a high specific power (i.e. light weight, compact and capable of storing and supplying high amounts of energy and power respectively). These batteries should also have a long life cycle (i.e. they should be able to discharge to as near as it can be to being empty and recharge to full potential as many number of times as possible) without showing any significant deterioration in the performance and should recharge in minimum possible time. They should be able to operate over a considerable range of temperature and should be safe to handle and recyclable with low costs. Unlike batteries used in traditional low power/energy applications, EV batteries require extra care in terms of safety since frequent fast charge/discharge cycles and high amounts of delivered power may cause excess heat generation. Advanced thermal management and cell balancing, plus the selection of an appropriate chemistry are all factors that affect cell losses. One passive solution is to use phase change materials, which remove large amounts of heat through latent heat of fusion [4].

Fig.1.3 shows the typical charging profile of Li-ion battery cell [5]. The common charging profiles used in the industry for Li-ion batteries are constant current (CC) and constant voltage (CV) charging. During CC charging the current is regulated at a constant value until the battery cell voltage reaches a certain voltage level. Then, the charging is switched to CV charging and the battery is charged with a trickle current applied by a constant voltage output of the charger.

![Fig.1.3 Typical charging profile of Li-Ion cell](image)

Fig.1.3 Typical charging profile of Li-Ion cell
1.1.2 Charger Classifications

Since the inception of the first EVs, there have been many different charging systems proposed. Due to many different configurations of the chargers, it is required to classify them based on some common design and application features. Table 1.1 [6] lists five different methods of classifying chargers.

Table 1.1: Battery charger classification

<table>
<thead>
<tr>
<th>Classification type</th>
<th>Options</th>
</tr>
</thead>
<tbody>
<tr>
<td>Topology</td>
<td>Dedicated, Integrated</td>
</tr>
<tr>
<td>Location</td>
<td>On-board, Off-board</td>
</tr>
<tr>
<td>Connection type</td>
<td>Conductive, Inductive, Mechanical</td>
</tr>
<tr>
<td>Electrical waveform</td>
<td>AC, DC</td>
</tr>
<tr>
<td>Direction of power flow</td>
<td>Unidirectional, Bidirectional</td>
</tr>
<tr>
<td>Power level</td>
<td>Level1, Level2, Level3</td>
</tr>
</tbody>
</table>

The chargers can be classified based on the circuit topologies [7]. A dedicated circuit solely operates to charge the battery. In comparison, the traction inverter drive can serve as the charger at the same time when the vehicle is not working and plugged into the grid for charging. This option is commonly known as integral/integrated chargers.

A second classification is the location of the charger. Carrying the charger on-board greatly increases the charging availability of the vehicle. Off-board chargers can make use of higher amperage circuits and can charge a vehicle in a considerably shorter amount of time.

Fig.1.4 Block diagram of off-board charger

For off-board charger shown in Fig.1.4 [7], the charger is an external unit, rather than a component of the EV. Furthermore an off-board charger produces a high DC voltage. The internal battery management system (BMS) must be able to charge the battery using this voltage. The major drawback of this topology is that the charger is not integrated in
the EV. Hence, it is impossible to charge the battery of an EV without an appropriate charger which provides the needed high DC voltage on-site.

![Fig.1.5 Block diagram of on-board charger](image)

For on-board charger shown in Fig.1.5 [7], the charger is a component of the EV. The EV can be charged almost everywhere using a single-phase or three-phase supply. The major drawback of this topology is that this simple on-board charger requires an additional DC/AC inverter. One inverter enables the vehicle-to-grid (V2G) capability and the second drives the AC propulsion machine.

Third is the connection method [8]. Conductive charging contains metal to metal contact, inductive charging connects ac grid to vehicle indirectly via a take-apart high frequency transformer, and mechanical charging replaces the depleted battery pack with a full one in battery swap stations.

Fourth, the electrical waveform at the connection port of the vehicle to the grid can be either a dc connection or an ac connection [6]. Currently, the PHEVs and EVs in the market employ an ac connection type. However, in the future the availability and commonality of the dc sources may change the connection type.

Fifth, the charger can deliver power in unidirectional way by just charging the battery. More advanced designs introduce bidirectional power transfer [9]. Again, all of the chargers in the market employ unidirectional chargers.

Last, three charging levels have been defined for EVs and PHEVs [10]. These are detailed in Table 1.2. Level 1 and level 2 charging are assumed to be the normal charging levels which will take place where the vehicle will sit for a substantial amount of time such as the home or office [11]. However, the drawback of charging a vehicle with these normal charging levels is that it can take 4 to 20 hours depending on available power, battery size and SOC of the battery [12] and this is not a viable option when long travel distances are considered. The solution to this lengthy charging time issue is the level 3 fast charging. Level 3 charging makes battery powered vehicles more competitive against
conventional ICE vehicles by charging the battery in less than 30 minutes [13]. Typically, level 3 charging is accomplished via an off-board charger by means of converting three-phase 480-V AC to a regulated DC. Although there have not been any adopted standards for level 3 charging in the US [14] or internationally other than Japan [15], a Japanese protocol known as CHAdeMO [16] is gaining international recognition. CHAdeMO supplies the vehicle with a regulated DC voltage requiring an external charging station, and interfaces directly with the vehicle battery and battery management system (BMS). Alternatively, several European automakers are focusing on supplying vehicles directly with 3-phase and processing it via an on-board battery charger [17].

<table>
<thead>
<tr>
<th></th>
<th>AC Voltage (V)</th>
<th>Max. Current (A)</th>
<th>Max. Power (kW)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Level 1</td>
<td>120</td>
<td>16</td>
<td>1.92</td>
</tr>
<tr>
<td>Level 2</td>
<td>240</td>
<td>80</td>
<td>19.2</td>
</tr>
<tr>
<td>Level 3</td>
<td>300-600</td>
<td>400</td>
<td>240</td>
</tr>
</tbody>
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### 1.2 Charger System

The charging time and lifetime of the battery have a strong dependency on the characteristics of the battery charger [18]-[20]. Several manufacturers are working worldwide on the development of various types of battery modules for electric and hybrid vehicles. However, the performance of battery modules depends not only on the design of modules, but also on how the modules are used and charged. In this sense, battery chargers play a critical role in the evolution of this technology.

![Battery charger system](image)

The conventional battery charger system is shown in Fig. 1.6 [44]. Because batteries have a finite energy capacity, PHEVs and BEVs must be recharged on a periodic basis, typically by connecting to the power grid. The charging system for these vehicles consists of an AC/DC rectifier to generate a DC voltage from the AC line, followed by a DC/DC converter to generate the DC voltage required by the battery pack. Additionally, advanced charging systems might also communicate with the power grid using power line...
communication (PLC) modems to adjust charging based on power grid conditions. The battery pack must also be carefully monitored during operation and charging in order to maximize energy usage and prolong battery life.

The focus of this thesis is to design and implement the DC-DC converter which charges the high-voltage battery.

1.3 Charger System Requirements for Isolated DC-DC Converters

In EV applications, the propulsion battery is required to undergo a continuous sequence of deep discharges followed by recharge to maximum capacity. The prime requirement is therefore a system that provides a rapid and efficient charge, using as simple equipment as possible and avoiding damage to the battery. The entire charging process should be arranged in two phases. The first charging phase is at constant current and with the battery voltage progressively rises. As soon as the battery voltage reaches the trickle level, the constant-voltage charging method should be applied, with the charging current progressively falling down to the maintenance level. The constant voltage charge phase requires a decoupled and very accurate (i.e., close to 1/1000) measure of the battery array voltage involving an expensive control system.

There are significant challenges associated with the design of the EV battery chargers, such as high power density, high efficiency, low cost, isolation and voltage adaption while complying with harsh environment automotive. Although the cost of passive elements can usually be decreased by simply increasing the switching frequency, frequency is mostly limited by the switching losses and turn on / turn-off time. Therefore, soft switching methods and resonant circuits are widely used to increase the switching frequency [21]. Operating from a high input voltage requires a soft transition topology to minimize the switching losses and reduce the high frequency EMI caused by a high $dv/dt$. Another challenge of such design is associated with the reverse recovery losses and the noise caused by the high $di/dt$ and $dv/dt$ in the output rectifiers. And also it is necessary to choose a topology that is also capable of controlling high output current.

In addition, galvanic isolation is required to disconnect grid from vehicle electrically. Galvanic isolation can be achieved by means of using a high frequency (HF) transformer integrated into DC-DC converter.
1.4 Conventional Isolated DC-DC Converters

1.4.1 Basic Isolated PWM Converters

The DC-DC converter topologies can be divided into two major parts: non-isolated and isolated converter as tabulated in Table 1.2 [35], depending on whether or not they have galvanic isolation between the input supply and the output circuitry. Isolated power converter topologies can be classified as either single-ended or double-ended depending on the usage of the B-H curve. During the operation, if the flux swings in only one quadrant of the B-H curve, then the topology is classified as single-ended. If the flux swings in two quadrants of the B-H curve, then the topology is classified as double-ended.

For a given set of requirements, a double-ended topology requires a smaller core than a single-ended topology and does not need an additional reset winding. When designing an isolated dc-dc power converter, the first and most critical choice is selection of the topology. Historically, topology selection was based upon the desired output power level. For the basic topologies, the order from lower power to higher power was usually flyback, forward, push-pull, half-bridge and full-bridge.

The flyback may be the most commonly used isolated topology. It is generally found in low cost, low power applications. Flyback topology requires only a single active switch and does not require a separate output inductor in addition to the transformer. This makes the topology easy to use and low cost. The disadvantages of the flyback topology are poor transformer utilization, as it is a single-ended topology, and extra capacitors are required at both the input and the output due to the high input and output ripple currents. The forward and active clamp forward topologies are often employed in medium power applications. The forward topology also suffers from poor transformer utilization due to the limited duty cycle and as it is also single-ended topology. The active clamp forward transformer does operate in two quadrants during steady state operation however peak flux can reach high levels during startup and transient conditions. In order to reset the transformer the maximum duty cycle is limited in both the forward topology and the active clamp forward topology.

The remaining three topologies; push-pull, half-bridge and full-bridge are true double-ended topologies whereby power transfer occurs in two quadrants of the BH curve and does not require special provisions to reset the transformer. These double-ended
topologies are the best choice for applications where the highest power density is desired, since the transformer core can be fully utilized. Another advantage of double-ended topologies is the transformer can be further optimized because of the larger available duty cycle range. Double-ended topologies can operate at a maximum duty cycle of almost 50% per side which equates to an effective maximum duty cycle of nearly 100% at the output filter inductor. Designing the transformer turns ratio to maximize the effective duty cycle greatly reduces the RMS current in the transformer and reduces the size of the output filter.

For push-pull topology configuration, diodes D1 and D2 are shown for simplicity however most modern, high efficiency power converters use synchronous MOSFETs as secondary rectifiers. The push-pull topology has the advantage of being double-ended however the peak voltage stress placed upon the primary switches during the off state is very high, well over two times the input voltage.

The advantage of the half-bridge over the push-pull is the primary switch voltage stress does not exceed the input voltage. Another advantage is there is only one primary winding, allowing the transformer core window to be better utilized. The half-bridge topology is only compatible with voltage-mode control. The $\frac{1}{2}V_{in}$ voltage balance at the midpoint between $C_1$ and $C_2$ is not maintained with current-mode control or when operating in cycle-by-cycle current limiting. Active midpoint balancing circuits can be added to allow a half-bridge to operate with current-mode control; however these circuits can be fairly complex.

For the full-bridge topology, it has all of the double-ended benefits. The primary switch voltage does not exceed the input voltage. Transformer window utilization is very good since there is only a single primary winding. When one of the primary switches is active for the Half-Bridge topology the voltage across the primary winding is $\frac{1}{2}V_{in}$. For the Full-Bridge topology, the switches are activated as diagonal pairs. When a pair of diagonal switches is active, the voltage across the primary winding is the full value of $V_{in}$. Therefore for a given power, the primary current will be half as much for the Full-Bridge as compared to the Half-Bridge. The reduced current enables higher efficiency as compared to a Half-Bridge especially at high load currents.
**Table 1.3: Power Supply Topologies from www.ti.com**

<table>
<thead>
<tr>
<th>Type of Converter</th>
<th>Flyback</th>
<th>Forward</th>
<th>2 Switch Forward</th>
<th>Active Clamp Forward</th>
</tr>
</thead>
<tbody>
<tr>
<td>Circuit Configuration</td>
<td><img src="image1" alt="Flyback Circuit" /></td>
<td><img src="image2" alt="Forward Circuit" /></td>
<td><img src="image3" alt="2 Switch Forward Circuit" /></td>
<td><img src="image4" alt="Active Clamp Forward Circuit" /></td>
</tr>
<tr>
<td>Ideal Transfer Function*</td>
<td>$\frac{V_{OUT}}{V_{IN}} = D \times \sqrt{\frac{L_p}{2 \times I_{OUT} \times L_p}}$</td>
<td>$\frac{V_{OUT}}{V_{IN}} = \frac{\frac{I_{OUT}}{N_p}}{1 - D}$</td>
<td>$\frac{V_{OUT}}{V_{IN}} = \frac{\frac{I_{OUT}}{N_p}}{1 - D}$</td>
<td>$\frac{V_{OUT}}{V_{IN}} = \frac{\frac{I_{OUT}}{N_p}}{1 - D}$</td>
</tr>
<tr>
<td>Drain Current*</td>
<td>$I_{DS (max)} = \frac{V_{IN} \times I_{OUT}}{TP}$</td>
<td>$I_{DS (max)} = \frac{V_{DS} \times I_{OUT}}{TP}$</td>
<td>$I_{DS (max)} = \frac{V_{DS} \times I_{OUT}}{TP}$</td>
<td>$I_{DS (max)} = \frac{V_{DS} \times I_{OUT}}{TP}$</td>
</tr>
<tr>
<td>Drain Voltage*</td>
<td>$V_{DS} = 2 \times V_{IN}$</td>
<td>$V_{DS} = V_{IN}$</td>
<td>$V_{DS} = V_{IN}$</td>
<td>$V_{DS} = V_{DS}$</td>
</tr>
<tr>
<td>Average Diode Current*</td>
<td>$I_{D1} = I_{OUT}$</td>
<td>$I_{D1} = I_{OUT} \times D$</td>
<td>$I_{D1} = I_{OUT} \times D$</td>
<td>$I_{D1} = I_{OUT} \times D$</td>
</tr>
<tr>
<td>Diode Reverse Voltage*</td>
<td>$V_{D1} = V_{IN} + V_{IN} \times \left(\frac{N_p}{N_p}\right)$</td>
<td>$V_{D1} = V_{IN} + V_{DS} \times \left(\frac{N_p}{N_p}\right)$</td>
<td>$V_{D1} = V_{IN} + V_{DS} \times \left(\frac{N_p}{N_p}\right)$</td>
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</tr>
</tbody>
</table>

**Voltage and Current Waveforms**

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* Excludes ripple current and output diode voltage drop. Continuous conduction mode shown unless otherwise noted. For

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**Type of Converter**

<table>
<thead>
<tr>
<th>HALF BRIDGE</th>
<th>PUSH PULL</th>
<th>FULL BRIDGE</th>
<th>PHASE SHIFT ZVT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Circuit Configuration</td>
<td><img src="image5" alt="Half Bridge Circuit" /></td>
<td><img src="image6" alt="Push Pull Circuit" /></td>
<td><img src="image7" alt="Full Bridge Circuit" /></td>
</tr>
<tr>
<td>Ideal Transfer Function*</td>
<td>$\frac{V_{OUT}}{V_{IN}} = \frac{\frac{I_{OUT}}{N_p}}{1 - D}$</td>
<td>$\frac{V_{OUT}}{V_{IN}} = \frac{\frac{I_{OUT}}{N_p}}{1 - D}$</td>
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</tr>
<tr>
<td>Drain Current*</td>
<td>$I_{DS (max)} = \frac{V_{DS} \times I_{OUT}}{TP}$</td>
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</tr>
<tr>
<td>Drain Voltage*</td>
<td>$V_{DS} = V_{IN}$</td>
<td>$V_{DS} = 2 \times V_{IN}$</td>
<td>$V_{DS} = V_{IN}$</td>
</tr>
<tr>
<td>Average Diode Current*</td>
<td>$I_{D1} = I_{OUT} \times D$</td>
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<tr>
<td>Diode Reverse Voltage*</td>
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</tr>
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</table>

**Voltage and Current Waveforms**

---

* Excludes ripple current and output diode voltage drop. Continuous conduction mode shown unless otherwise noted.
The disadvantage of the full-bridge topology is the added complexity of driving four primary switches and the cost of the additional switches. Relative to the Half-Bridge, part of this additional cost is offset with reduction of input capacitors.

Another full-bridge configuration, which is used in high input voltage and high power applications, is the phase-shifted full-bridge. This topology is similar to the conventional full-bridge. However, the control methodology is different; the phase-shifted Full-Bridge (PSFB) results in zero-voltage transitions of the primary switches while keeping the switching frequency constant. Zero-volt switching is especially beneficial at high input voltage applications. Often this topology needs an extra commutating inductor in series with primary of the power transformer to ensure zero-volt switching at light load conditions. A disadvantage of this topology is increased conduction losses in the primary during the freewheeling time.

1.4.2 Basic Resonant Converters

Resonant converter, which were investigated intensively in the 80's [36]-[43], can achieve very low switching loss thus enable resonant topologies to operate at high switching frequency. In resonant topologies, Series Resonant Converter (SRC), Parallel Resonant Converter (PRC) and Series Parallel Resonant Converter (SPRC, also called LCC resonant converter) are the three most popular topologies. The analysis and design of these topologies have been studied thoroughly.

1) Series Resonant Converter

The circuit diagram of a half bridge Series Resonant Converter is shown in Fig.1.7 (a) [45]-[50] and the gain curve of SRC is shown in Fig.1.7 (b). The resonant inductor \( L_r \) and resonant capacitor \( C_r \) are in series. They form a series resonant tank. The resonant tank will then in series with the rectifier-load network. In this configuration, the resonant tank and the load act as a voltage divider. By changing the frequency of driving voltage \( V_d \), the impedance of resonant tank will change. The input voltage is split between this impedance and the reflected load. Since it is a voltage divider, the DC gain of SRC is always lower than 1. At light-load condition, the impedance of the load is very large compared to the impedance of the resonant network; all the input voltage is imposed on the load. This makes it difficult to regulate the output at light load. Theoretically, frequency should be infinite to regulate the output at no load.
When switching frequency is lower than resonant frequency, the converter will work under zero current switching (ZCS) condition. When switching frequency is higher than resonant frequency, the converter will work under zero voltage switching (ZVS) condition. For power MOSFET, zero voltage switching is preferred. It can be seen from the operating region that at light load, the switching frequency need to increase to very high to keep output voltage regulated. This is a big problem for SRC. To regulate the output voltage at light load, some other control method has to be added. As input voltage increases, the converter is working at higher frequency away from resonant frequency.

As frequency increases, the impedance of the resonant tank is increased. This means more and more energy is circulating in the resonant tank instead of transferred to output. Here the circulating energy is defined as the energy send back to input source in each switching cycle. The more energy is sending back to the source during each switching cycle, the higher the energy needs to be processed by the semiconductors, the higher the conduction loss. Also the turn off current is much smaller at lower input. When input voltage increases, the turn off current is increased.

With above analysis, we can see that the major problems of SRC are: light load regulation, high circulating energy and turn off current at high input voltage condition.

2) **Parallel Resonant Converter**

The schematic of parallel resonant converter is shown in Fig. 1.8 (a) [51]-[54] and its gain curve is shown in Fig. 1.8 (b). For parallel resonant converter, the resonant tank is still in series. It is called parallel resonant converter because in this case the load is in parallel with the resonant capacitor. More accurately, this converter should be called series resonant converter with parallel load. Since transformer primary side is a capacitor, an inductor is added on the secondary side to match the impedance.
Fig.1.8 Half Bridge PRC

From the gain curves in 1.8 (b), Similar to SRC, the operating region is also designed on the right hand side of resonant frequency to achieve Zero Voltage Switching. Compare with SRC, the operating region is much smaller because the mountain is much steeper. At light load, the frequency doesn't need to change too much to keep output voltage regulated. So light load regulation problem doesn't exist in PRC. At high input voltage, the converter is working at higher frequency far away from resonant frequency. Also from the MOSFET current we can see that the turn off current is much smaller at lower input.

Compare with SRC, it can be seen that for PRC, the circulating energy is much larger. For PRC, a big problem is the circulating energy is very high even at light load. Since the load is in parallel with the resonant capacitor, even at no load condition, the input still see a pretty small impedance of the series resonant tank. This will induce pretty high circulating energy even when the load is zero.

The major problems of PRC are: high circulating energy, high turn-off current at high input voltage condition.

3) Series Parallel Resonant Converter

The schematic of series parallel resonant converter is shown in Fig.1.9 (a). [55]- [57] and the gain curve of SPRC is shown in Fig.1.9 (b). Its resonant tank consists of three resonant components: \( L_r \), \( C_{sr} \) and \( C_{pr} \). The resonant tank of SPRC can be looked as the combination of SRC and PRC. Similar as PRC, an output filter inductor is added on secondary side to match the impedance. For SPRC, it combines the good characteristic of PRC and SRC. With load in series with series tank \( L_r \) and \( C_{sr} \), the circulating energy is smaller compared with PRC. With the parallel capacitor \( C_{pr} \), SPRC can regulate the output voltage at no load condition.
Similar to SRC and PRC, the operating region is also designed on the right hand side of resonant frequency to achieve Zero Voltage Switching. From the operating region graph, it can be seen that SPRC narrow switching frequency range with load change compare with SRC.

The input current is much smaller than PRC and a little larger than SRC. This means for SPRC, the circulating energy is reduced compare with PRC.

Same as SRC and PRC, at high input voltage, the converter is working at higher frequency far away from resonant frequency. Same as PRC and SRC, the circulating energy and turn off current of MOSFET also increase at high input voltage.

With above analysis, we can see that SPRC combines the good characteristics of SRC and PRC. Smaller circulating energy and not so sensitive to load change.

Unfortunately, SPRC still will see big penalty with wide input range design. With wide input range, the conduction loss and switching loss will increase at high input voltage. The switching loss is similar to that of PWM converter at high input voltage.

These three converters all cannot be optimized at high input voltage. High conduction loss and switching loss will be resulted from wide input range.

4) LLC Resonant Converter

Three traditional resonant topologies analyzed above have a major penalty for wide input range design. High circulating energy and high switching loss will occur at high input voltage. There are some lessons learned from the above analyses. For a resonant tank, working at its resonant frequency is the most efficient way. This rule applies to SRC and PRC very well. For SPRC, it has two resonant frequencies. Normally, working at its highest resonant frequency will be more efficient.
To achieve zero voltage switching, the converter has to work on the negative slope of DC characteristic. From above analysis, SPRC resonant converter also could not be optimized for high input voltage. The reason is same as for SRC and PRC; the converter will work at switching frequency far away from resonant frequency at high input voltage. Look at DC characteristic of SPRC resonant converter, it can be seen that there are two resonant frequencies. One low resonant frequency determined by series resonant tank $L_r$ and $C_{sr}$. One high resonant frequency determined by $L_r$ and equivalent capacitance of $C_{sr}$ and $C_{pr}$ in series. For a resonant converter, it is normally true that the converter could reach high efficiency at resonant frequency. For SPRC resonant converter, although it has two resonant frequencies, unfortunately, the lower resonant frequency is in ZCS region. For this application, we are not able to design the converter working at this resonant frequency. Although the lower frequency resonant frequency is not usable, the idea is how to get a resonant frequency at ZVS region. An LLC resonant converter could be configured in Fig.1.10 (a) [58]-[60]. The DC characteristic of LLC converter is like a flip of DC characteristic of SPRC resonant converter. There are still two resonant frequencies. In this case, $L_r$ and $C_r$ determine the higher resonant frequency. The lower resonant frequency is determined by $C_r$ and the series inductance of $L_{pr}$ and $L_{sr}$. Now the higher resonant frequency is in the ZVS region, which means that the converter could be designed to operate around this frequency.

Applications in which the LLC converter is used can take advantage of these two main features:

a. Narrow switching frequency range with light load and ZVS capability with even no load, thus very low switching losses (high efficiency).

b. The capability to control the output voltage at all load and line conditions.
1.5 Topology Selection for EV Battery Charger

A topological overview of the different configurations used in EV power conversion systems and general system block diagrams are presented in [61]-[65]. For the DC-DC stage, many topologies can be considered as candidates. Among them, the most attractive topologies are [22]-[24]:

1) A soft-switched full-bridge (FB) DC-DC converter;
2) An asymmetrically controlled zero-voltage switched (ZVS) half-bridge (HB) converter;
3) An active-clamped soft-switched forward converter.

All these three DC-DC converters can achieve very high efficiency and very good device utilization. Further selection of the dc-dc converter will depend on application specifications, including power level, input line voltage, battery voltage, initial capital cost, long term operation expense, and some economics and business philosophy.

Resonant converters are included in a wide range of converters. The strategy of using one is to design a highly efficient converter while eliminating a common disadvantage of traditional implementations based on Pulse-Width Modulation (PWM) – high switching losses. Many different solutions have been suggested, implemented, and tested in recent years, and many of them are now widely used in commercial products. Different battery chargers based on resonant topologies have been reported in [25]–[27]. Generally speaking, in order to guarantee ZVS in resonant converters, a high value of reactive current circulation is required, particularly for a wide range of load variations. This leads to a bulky resonant tank, lower power density, and lower efficiency.

Auxiliary commutated ZVS full-bridge converter topologies suitable for low-power applications have been reported in [28] and [29] and further developed in [30]. In these converters, an auxiliary circuit is used to produce the reactive current for the full-bridge switches. The auxiliary circuit is working independent of the system operating conditions and is able to guarantee ZVS from no load to full load. Although this topology seems very suitable for the battery charger application, there are some setbacks related to the auxiliary circuit. Since the auxiliary circuit should provide enough reactive power to guarantee ZVS at all operating conditions, the peak value of the current flowing through the auxiliary inductor is very high, which increases the MOSFET conduction losses drastically. Also,
due to the fact that the voltage and frequency across the auxiliary inductor are very high, the core losses of this inductor are also high. In addition, too much reactive current leads to large voltage spikes on the semiconductor switches due to the delay in the body diode turn-on. [31] presents a control method, which optimizes the required reactive current provided by the auxiliary circuit. The proposed control circuit adaptively controls the reactive current required to guarantee ZVS under different load conditions. This leads to significantly reduced semiconductor conduction losses as well as reduced auxiliary circuit losses.

This thesis works on the power stage, presenting a hybrid phase-shifted full-bridge and LLC resonant converter, which guarantees ZVS under any load conditions, and then gets it further improved. This hybrid converter can achieve ZVS operation in the entire load range by using the magnetizing inductance of the transformer. In addition, the converter can operate with wide input-voltage variations without penalizing the efficiency. Therefore, the converter is suitable for applications in which high efficiency and high power density are required such as EV battery charger.

1.6 Thesis Outline

This thesis is divided into four chapters. They are organized as follows.

The first chapter is background of battery charger. Since the DC-DC converter is the key element in battery charger system and this thesis mainly deals with the DC-DC converter for EV battery charger, the isolated DC-DC converters are also simply overviewed.

In second chapter, two basic types of DC-DC converters, which are applied in high power application such as high voltage battery for electric vehicle, are analyzed theoretically in detail.

The third chapter gives the novel converter topology for EV battery charger and its corresponding detailed analysis. A 3.4 kW hardware prototype for battery charger has been designed, fabricated and tested to verify the circuit validity and the improved performance of the proposed converter.

In fourth chapter, an improved converter based on the one in chapter3 is developed and analyzed theoretically.
2.1 Introduction

In this chapter, two basic types of DC-DC converters, which are applied in high power application such as high voltage battery for electric vehicle, are analyzed theoretically in detail.

The full-bridge and half-bridge converters are mostly used in high power applications. In both converters, the input voltage appears across the switching transistors. However, they are required to carry twice as much current in the half-bridge converter. Therefore, in high power applications, it may be advantageous to use a full bridge over a half bridge.

Efficiency, power density, reliability, and cost are important for the switched mode power supply market. The effort to obtain ever-increasing power density of switched-mode power supplies has been limited by the size of passive components. Operation at higher frequencies considerably reduces the size of passive components, such as transformers and filters. In order to achieve converters with high power densities, it is usually required that they operate at higher switching frequencies. However, the high transistor switching frequencies increase the total switching loss and lower the supply efficiency. As switching frequencies increase, the switching losses associated with the turn-on and turn-off of the devices also increases.

Therefore, zero voltage or zero current switching topologies allow for high frequency switching while minimizing the switching loss. The ZVS topology operating at high frequency can improve the efficiency and reduce the size and cost of the power supply resulting in higher power densities. ZVS also reduces the stress on the semiconductor switch, which improves the converter reliability. The Phase-Shifted ZVS Full Bridge DC/DC Converter has become a very popular topology due to above advantages. [32]-[33]analyzed the operation of the phase shift full bridge (PSFB) ZVS dc-dc converter. The major problems are the high circulating current during normal operation, hard switching on the secondary side and light load efficiency. In addition, due to duty cycle loss problem, the effective duty cycle is even smaller. More conduction loss deteriorates the efficiency.
On the other hand, although soft switching is achieved at the primary side, hard switching problems still remain for the secondary side devices. Switching loss and voltage stress of secondary side devices are severe issues. At light-load conditions, ZVS may be lost. Thus, the efficiency under light loads is another concern.

To reduce switching losses and allow high-frequency operation, resonant switching techniques have been developed. In switch-mode PWM power supplies, the switching losses can be high enough that they prohibit the operation of the power supply at very high frequencies, even when soft-switching techniques are used. In resonant-mode power supplies, however, the switching losses can be lower, allowing the resonant converter to operate at higher frequencies [34]-[35]. Therefore, the use of resonant converters remains an interesting option for some applications requiring high efficiency, high reliability, high power density and low cost. These techniques process power in a sinusoidal manner and the switching devices are softly commutated. Therefore, the switching losses and noise can be dramatically reduced. For conventional PWM converters, LLC resonant converter becomes the most attractive topology for medium power applications due to its high efficiency and wide input range.

In general, LLC resonant converter can be employed in all applications with variable input and output voltages, demand of high efficiency and power density as well as low EMI. It exhibits superior performance, such as low switching loss and low voltage stress on the secondary side rectifiers, as well as higher efficiency, than PWM converters. LLC resonant converters can achieve ZVS from zero load to full load conditions. The LLC resonant tank can be considered as a band pass filter, but the frequency selectivity of the LLC tank is poor. For a resonant tank, working at its resonant frequency is the most efficient way. Due to very wide bandwidth, the frequency has to be increased very high to achieve enough voltage gain controllability. However, this is not practical for DC-DC converters due to the limitation of driving circuits and the excessive switching & driving losses.

Although there are some disadvantages in these two kinds of converters, they are widely used in high power application. Next, the conventional phase shifted full bridge converter and LLC converter will be discussed in detail in the following sections.
2.2 Phase Shifted Full Bridge Converter

When conventional PWM converters are operated at higher frequencies, the circuit parasitics are shown to have detrimental effects on the converter performance. Switching losses are especially pronounced in high-power, high-voltage applications. To achieve ZVS, the two legs of the bridge are operated with a phase shift. This operation allows a resonant discharge of the output capacitance of the MOSFETs, and, subsequently, forces the conduction of each MOSFET’s anti-parallel diode prior to the conduction of the MOSFET. It provides ZVS for the switches by using the leakage inductance of the transformer and the output capacitance of the switches. It has a somewhat higher rms current than the conventional full-bridge PWM converter, but has much lower rms currents than the resonant converters. The ZVS allows operation with much reduced switching losses and stresses, and eliminates the need for primary snubbers. It enables high switching frequency operation for improved power density and conversion efficiency. These advantages make this converter well suited for high-power, high-frequency applications.

2.2.1 Topology Description

Phase shift full bridge converter shown in Fig.2.1, as one of the most promising topology for high frequency, high power application, has many good characteristics. It is a soft switching converter. All four switches on primary side can achieve Zero Voltage Switching (ZVS) with proper design. This is very helpful for high frequency operation. This topology has lower volt-sec on the output filter inductor. Phase shift full bridge can
achieve smallest volt-sec for same design specification compared with two-switch forward and half bridge converter. Another benefit of phase shift full bridge is its capability to cover wide power range. For power from several hundred watts to kilowatts, full bridge converter can perform very well. In recent years, even for low power application like Voltage Regulator Module, full bridge topology has been investigated and showed benefits.

![Diagram showing the difference between regular Full Bridge and PH-Full Bridge ZVS PWM DC/DC converter topologies](image)

The conventional full-bridge topology is switched off under hard switching conditions where switch voltage stress is also high. The conventional full bridge topology has been modified in two ways to achieve ZVS. First, modulation is done by phase shifting two overlapping constant frequency square waves by using leading-leg and lagging-leg. Second, ZVS is achieved to minimize or reduce the switching losses. The primary difference between this topology and the traditional full-bridge topology is switching method as shown in Fig.2.2.

In contrast to turning on the diagonally opposite switches of the bridge simultaneously (i.e. S1 & S4, S2 & S3), a phase shift is introduced between the switches in the left leg (lagging-leg S3 & S4) and those in the right leg (leading-leg S1 & S2). The phase shift determines the operating duty cycle of the converter. The DC bus voltage is applied to transformer primary and power is transferred when two diagonal MOSFETs are on.
simultaneously. When two high side switches or two low side switches are on simultaneously (called freewheel state) the transformer primary is shorted. This results in zero voltage across primary and secondary. The transformer primary current rising edge slope as well as the falling edge slope reduces the duty cycle of the secondary voltage. This reduces the output voltage of the DC/DC converter so transformer turns ratio is effected and hence the secondary side power devices voltage. $L_{lk}$ and $L_o$ affect this so their values should be selected properly and effect should be analyzed.

### 2.2.2 Operating Modes

The schematic and operating waveforms of phase shift full bridge converter are repeated in Fig.2.3. Based on this, operating modes are given.

![Fig.2.3 Phase-shifted Full bridge converter](image)

1) At time $t_1$

- S₄ turns off, S₃ turns on, and S₂ remains on.
- The equivalent capacitor $C_{s₃}$ of S₃ gets sinusoidal discharged and the equivalent capacitor $C_{s₄}$ of S₄ gets sinusoidal charged by the leakage inductor ($L_{lk}$) current which is relatively small. Thus, these two capacitors $C_{s₃}$ and $C_{s₄}$ are much harder to get fully charged and discharged. S₃ and S₄ are much harder to be turned on at zero-voltage condition. These two switches S₁, S₂ form the lagging leg in the circuit.
- The 4 diodes at the secondary side conduct.
- The transformer is shorted.
2) At interval $t_1 \sim t_2$
- The equivalent capacitor of $S_3$ gets fully discharged and the equivalent capacitor of $S_4$ gets fully charged. To make sure the equivalent capacitors get fully charged and discharged, it requires a period of time during which both $S_3$ and $S_4$ are off. The period is called dead time.
- The body diode $D_3$ of $S_3$ is on, which can make $S_3$ turn on at zero-voltage condition.
- The 4 diodes at the secondary side are still conducting.
- The transformer is still shorted.

3) At interval $t_2 \sim t_3$
- $L_{in}$ is charged.
- The primary current switches from $D_2$-$D_3$ to $S_3$-$S_2$.
- The 4 diodes at the secondary side are still conducting.
- The transformer is still shorted.
4) At interval $t_3$~$t_4$

- $L_{lk}$ keeps charged.
- The output inductor $L_o$ gets charged and the voltage at the secondary side $v_{sec}$ builds up.
- The energy is transferred to output load. This is power processing stage.
- The 2 diodes at the secondary side are conducting.

5) At interval $t_4$

- $S_2$ is turned off, $S_1$ is turned on and $S_3$ is still on.
- The equivalent capacitor ($C_{s1}$) of $S_1$ gets linear discharged and the equivalent capacitor ($C_{s2}$) of $S_2$ gets linear charged by the output inductor ($L_o$) current which is relatively large. Thus, these two capacitors $C_{s1}$ and $C_{s2}$ are much easier to get fully charged and discharged. $S_1$ and $S_2$ are much easier to be turned on at zero-voltage condition. These two switches $S_1$, $S_2$ form the leading leg in the circuit.
- The voltage at the secondary side $v_{sec}$ drops. The circuit is going to freewheeling stage from power processing stage.
- The 2 diodes at the secondary side are conducting at this moment.
6) At interval $t_4-t_5$

- The equivalent capacitor of $S_1$ gets fully discharged and the equivalent capacitor of $S_2$ gets fully charged. To make sure the equivalent capacitors get fully charged and discharged, it requires dead time between $S_1$ and $S_2$.
- The body diode $D_1$ of $S_1$ is on, which can make $S_1$ is turned on at zero-voltage condition.
- The voltage at the primary side $v_{pri}$ is clamped to zero.
- The 4 diodes at the secondary side are conducting.

In order to avoid shoot through and ensure that $S_4$ will turn-on with ZVS a dead time is needed between the turn-off of $S_3$ and turn-on of $S_4$ and also make sure that diode $D_4$ has started conducting. The resonance between $L_{lk}$, $C_s$ ($C_{s3} // C_{s4}$) and $C_{tr}$ provides sinusoidal voltage across $S_3$ and $D_3$ and this voltage peaks at one fourth of the resonant period.

$$
\tau_{peak} = \frac{1}{4} T = \frac{\pi}{2} \sqrt{L_{lk} \left( C_{s3} // C_{s4} // C_{tr} \right)}
$$

(2.1)
2.2.3 ZVS Process

Zero-voltage turn-on is achieved by using the energy stored in the leakage and series inductance of the transformer to discharge the output capacitance of the switches through resonant action. In order to achieve ZVS turn-on the energy stored in the leakage and series inductance has to be larger than the energy stored in the output capacitances. The resonance forces the body diode into forward conduction prior to gating on the switch. Two different mechanisms exist which provide ZVS for the lagging-leg and leading leg.

a. ZVS for Lagging Leg

![Diagram of ZVS for Lagging Leg](image)

Fig. 2.10 Detail of the rising edge of the voltage across the switch of lagging leg where

(a) corresponds to the limit case when the energy in $L_{lk}$ is equal to the energy required to charge the capacitances.

(b) corresponds to the case when the energy in $L_{lk}$ is larger than the energy required to charge/discharge the capacitors. The switch output capacitances are charged/discharged in less than one fourth of the resonant period, and the voltage is clamped to the input voltage.

(c) corresponds to the case when the energy in $L_{lk}$ is not sufficient to charge/discharge the output capacitances, and ZVS is lost.

During light loads, very little energy is stored in the primary side inductance $L_{lk}$ (can be sum of the transformer leakage inductance and external inductance in series with the primary of the transformer). This causes the lagging-leg to turn on under a hard switching condition which can be seen from Fig. 2.10 (c) and Loss of ZVS means extremely high
switching losses at high switching frequencies and very high electromagnetic interference (EMI) due to the high $di/dt$ of the discharge current. Loss of ZVS can also cause a very noisy control circuit, which leads to shoot-through and loss of the semiconductor switches. As the load increases the energy stored in inductor $L_{lk}$ increases. This energy is used to charge the output capacitance of the devices that are turning off, and to discharge the output capacitance of the complementary device, thus forward biasing the freewheeling diode. Full output capacitive discharge is necessary to cause the lagging-leg to start turning-on under the ZVS condition. The turn-off under the ZVS condition closely mimics that of resistive turn-off. A switch with low output capacitance helps to achieve ZVS process at light load, improving the efficiency. Hard switching occurs when the output capacitance of the switch requires more energy than is available in the inductance $L_{lk}$ to fully charge and discharge the switches. And the energy stored available to turn on lagging-leg the diode is very small so its conduction time is very small even at full load. The energy stored in $L_{lk}$ increases by a square law as load current increases. Therefore, the stored energy in $L_{lk}$ increases rapidly at loads higher than the minimum load required for ZVS. The large amount of available charging energy causes the switch drain-source voltage to rise and fall at a linear rate.

To achieve soft turn-on and turn-off of the lagging leg, the following equation should be satisfied.

$$\frac{1}{2} L_{lk} I_1^2 > \frac{1}{2} (C_{s3} + C_{s4}) V_{in}^2 + \frac{1}{2} C_{tr} V_{in}^2$$  \hspace{1cm} (2.2)$$

Where $C_{s3}, C_{s4}$ is effective output capacitance of the power switches $S_3, S_4$ respectively. $I_1$ is Primary transformer current at turn-on and turnoff for $S_3 & S_4$. $C_{tr}$ is transformer winding capacitance.

Thus, the critical load at which ZVS is lost is

$$I_{ZVS} = \sqrt{\frac{C_{s3} l / C_{s4} + C_{tr}}{L_{lk}} V_{in}}$$  \hspace{1cm} (2.3)$$

To make sure not to lose ZVS, the leakage inductance is adjusted to obtain a desired value of $I_{ZVS}$
The lagging leg switch transition occurs due to resonance. The primary current during this transition is sinusoidal with peak amplitude occurring at the start. $C_s (C_{s3} // C_{s4})$ and $L_{lk}$ form the resonant tank and its oscillating frequency is given as follows.

$$\omega_r = \frac{1}{\sqrt{L_{lk} (C_{s3} // C_{s4})}}$$  \hspace{1cm} (2.4)

There must be enough time to get the output capacitor of the to-be turned on switch fully discharged to make sure the switch can operate at ZVS condition. Meanwhile, the discharge time should not be too long in case of another oscillating cycle starts, which is clear in Fig.2.10 (b). The maximum discharge is at $1/4$ of the period as follows, which is also graphically shown in Fig.2.10 (a).

$$t_d^{\text{max}} = \frac{1}{4} T = \frac{\pi}{2} \sqrt{L_{lk} (C_{s3} // C_{s4} // C_{tr})}$$  \hspace{1cm} (2.5)

b. ZVS for Leading Leg

For the leading-leg switches (S1& S2), a different process provides the ZVS as explained below. Before S1 turns off, the current in the primary reaches its peak value of the reflected filter inductor ($L_o$) current. When S1 is turned off, the energy available to charge the output capacitance of S1 and to discharge the output capacitance of S2 is the sum of the energy stored in the output filter inductor $L_o$ and the primary side inductor $L_{lk}$. The energy stored in filter inductor $L_o$ is available because the filter inductor current does not freewheel through the diode until the voltage across the secondary has fallen to zero.

![Fig.2.11 Detail of the rising edge of the voltage across the switch of leading leg](image)

Accordingly, for soft turn on and turn-off of the leading leg the following equation should satisfy.
where \( C_{s1}, C_{s2} \) is effective output capacitance of the power switches \( S_1, S_2 \) respectively. \( I_2 \) is Primary transformer current at turn-on and turnoff for \( S_1 \& S_2 \). \( C_p \) is transformer winding capacitance. \( L_{os,p} \) is the output filter inductance referred to primary.

Since the stored energy in the output filter inductor is large when compared to that required to charge and discharge the output capacitances of the leg and capacitance of the transformer windings, the switch capacitance is charged and discharged at a linear rate. The resulting leading leg transition time in liner ramp is given as

\[
I_2 = C_s \frac{dv}{dt} \quad \text{or} \quad dt = C_s \frac{dv}{I_2} \quad (2.7)
\]

Where \( I_2 = C_s \frac{dv}{dt} \) or \( dt = C_s \frac{dv}{I_2} \)

\( dv = V_{in} \), which is input to the bridge and \( dt \) is switch transition time.

In this mode, even at lighter loads, much more stored energy is available to turn-on and turn-off the leading-leg switches than is available for the lagging leg switches. Therefore, the body diode in the leading leg turns on before the MOSFET is gated on even at light loads. Since the energy stored in output filter is so high that a small snubber capacitor can be put across leading leg switches and these devices can be turned off under real ZVS condition. This will reduce the turn-off loss of these switches. The leading leg free-wheeling diode (FWD) conduction duty cycle is higher than lagging led diodes so leading-leg diodes will also dissipate a fair amount of power.

### 2.2.4 Relation between Duty Cycle, Transformer Turns Ratio and Switching Frequency

Fig. 2.12 shows the relationship between duty cycle, transformer turns ratio and switching frequency for the phase-shifted full bridge converter.

\[
\begin{align*}
D_{sec} &= \frac{N V_o}{V_{in}} \\
D_{off} &= D_{sec} = D_{pul} - \Delta D \\
\Delta D &= \left( \frac{V_{in}}{T L_{ik}} \right) = D_{sec} \frac{4I_{ik}}{N^2 R_o f_s}
\end{align*}
\]  

(2.8)
where \( N \) is the primary-to-secondary turns ratio; \( D_{\text{eff}} \) is effective duty cycle on the secondary, that is \( D_{\text{sec}} \); \( \Delta D \) is called duty cycle loss. Increasing \( L_{\text{pk}} \) or \( f_s \) will increase \( \Delta D \). And since \( \Delta D \) cannot exceed \( D_{\text{sec}} \) and \( D_{\text{sec}} + \Delta D < D_{\text{pri, max}} < 1 \), there is a limit on the switching frequency. Although some drawbacks for phase shift full bridge, it is still a popular topology. Its capability to operate at high frequency and wide power range enable it to be used for multi applications.

\[
\text{Fig.2.12 Relation between duty cycle, transformer turns ratio and switching frequency}
\]

### 2.2.5 Disadvantages of Phase-shifted Full Bridge Converter

\[
I_i \geq I_{\text{ZVS}} = \sqrt{\frac{C_{\text{ss}}}{C_{\text{ss}} + C_{\text{ve}}} V_{\text{in}}} \frac{4L_{\text{pk}}}{N^2 R_{\text{o}} f_s}
\]

\[
\Delta D = D_{\text{sec}} \frac{4L_{\text{pk}}}{N^2 R_{\text{o}} f_s}
\]

\[
\text{Fig.2.13 Key waveforms and formula of conventional PSFB converter}
\]

**ZVS FULL-BRIDGE** topology is the most popular topology used in the power range of a few kilowatts (1–5 kW) for DC/DC converters [31]. Since the switch ratings are optimized for the full-bridge topology, this topology is extensively used in industrial applications. High efficiency, high power density, and high reliability are the prominent features of this topology. But since ZVS in conventional full-bridge pulse width modulation (PWM) converters is achieved by utilizing the energy stored in the leakage
inductance to discharge the output capacitance of the MOSFETs, the range of the ZVS operation is highly dependent on the load and the transformer leakage inductance. It is difficult to design a wide-operation-range PWM converter with high efficiency. According to the key waveforms shown in Fig.2.13 of the phase-shifted full bridge converter, the disadvantages are summarized as follows.

- It is not able to ensure ZVS operation at light loads. In battery charger applications, ZVS is vitally important since the converter might be operating at absolutely no load for a long period of time. In this application, when the battery is charged, the load is absolutely zero, and the converter should be able to safely operate under the zero-load condition.

- The magnitude of $L_{lk}$ of the transformer determines the ZVS load range and the ZVS range can be extended by increasing the leakage inductance $L_{lk}$. Since $L_{lk}$ limits the rising and falling times of the primary currents, the available duty cycle in the secondary is reduced. A large leakage inductance limits the power transfer capability of the converter and reduces the effective duty ratio of the converter. This limits the maximum $L_{lk}$ to be used in a particular design.

- The transformer turns ratio $N_s/N_p$ can be maximized to reduce the voltage stress of the rectifiers. However, increasing $N_s/N_p$ reduces the primary current and consequently increases the value of the $L_{lk}$ required for achieving a desired ZVS range.

- There is a limit on the switching frequency. Increasing the switching frequency also increase the duty cycle loss.

- It has high circulating current during normal operation. During every switching cycle, there is a time interval during which two up switches or low switches are turned on at the same time. This will short the transformer primary side. During this time interval, secondary is freewheeling and no energy transfer from input to output. Primary current during this period is pretty high. This current circulates through the primary two switches and transformer winding. This primary circulating current will increase conduction loss and should be minimized to achieve high efficiency. The smaller the duty cycle, the higher circulating current will be.
Due to ZVS operation the primary side waveforms are free from switching noise and require no snubber. The secondary voltage waveform for a high output voltage (360 V) has a substantial ringing due to the reverse recovery of the diodes. The ringing frequency is usually too close to the switching frequency which makes it difficult to snub the ringing effectively using a RC snubber. An energy recovery snubber network is employed to keep the snubber loss below 1% of the output power.

2.3 LLC Resonant Converter

Fig.2.14 shows the circuit configuration of half bridge LLC resonant converter. With variable frequency control, the voltage gain of LLC resonant converter can be controlled as boost mode or buck mode. During the holdup time, the LLC resonant converter can operate in boost mode. Thus, high voltage gain is achieved, which means that bulky capacitors can be reduced considerably. Meanwhile, at the nominal condition, the LLC resonant converter operates very close to the resonant frequency, which is the best operation point to accomplish high efficiency. In addition, voltage gains of different Q converge at the series resonant point. The LLC resonant tank parameters can be optimized to achieve high efficiency for a wide load range. The LLC resonant converter is considered as one of the most desirable topologies for wide input voltage range.

![Fig.2.14 Half Bridge LLC Resonant Converter](image)

LLC resonant converter has small switching loss. In LLC resonant converter, magnetizing inductor current is used to realize ZVS and ZVS can be achieved from the zero load to the full load conditions with small turnoff current. Therefore, zero turn-on loss and small turn-off loss can be achieved. Furthermore, secondary side diode of LLC resonant converter turns off with low $\frac{di}{dt}$. Thus, reverse recovery loss can be small on
secondary side. Combining smaller switching loss on both primary and secondary side, LLC resonant converter efficiency is not sensitive to the switching loss and the circuit is able to achieve high switching frequency operation.

Suppose \( N_p / N_s = 1 \), by using the same previous method discussed before, the equivalent circuit for LLC in Fig.2.15 can be obtained and the voltage gain, \( M \), can be derived.

![Fig.2.15 Equivalent Circuit for Half Bridge LLC Resonant Converter](image)

By using the equivalent load resistance, the LLC AC equivalent circuit is obtained, as illustrated in Fig.2.16 (a) and Fig.2.16 (b) shows how to obtain the equivalent load resistance, \( R_{ac} \).

![Fig.2.16 LLC Equivalent Circuit](image)

By using exactly the same method as that applied in SRC, \( R_{ac} = \frac{V_{ao,F}}{I_{ac}} = \frac{8}{\pi^2} R_o \)

(Considering the transformer turns ratio \( n = N_p / N_s \), the equivalent load resistance is \( R_{ac} = \frac{V_{ac,F}}{I_{ac}} = \frac{8n^2}{\pi^2} R_o \), and according to the LLC AC equivalent circuit of Fig.2.16 (a), the LLC voltage gain, \( M \), is obtained as:

\[
M = \frac{V_o}{V_{in}/2} = \frac{V_{ac, pk}}{v_{d, pk}} = \frac{4}{\pi} \left( \frac{\omega}{\omega_o} \right)^2 (m-1) \left( \frac{\omega^2}{\omega_p^2} - 1 \right) + j \frac{\omega}{\omega_o} \left( \frac{\omega^2}{\omega_p^2} - 1 \right) (m-1) Q
\]

where \( L_p = L_m + L_r, m = \frac{L_p}{L_r}, Z_r = \sqrt{\frac{L_r}{C_r}}, Q = \frac{Z_r}{\frac{R_{ac}}{\omega_o}}, \omega_o = \frac{1}{\sqrt{L_r C_r}}, \omega_p = \frac{1}{\sqrt{L_p C_r}}. \)
The gain curve is plotted in Fig.2.17 for different $Q$ values as follows.

For this converter, there are two resonant frequencies. One is determined by the resonant components $L_r$ and $C_r$. The other one is determined by $L_m$, $C_r$ and load condition. As load getting heavier, the resonant frequency will shift to higher frequency. The two resonant frequencies are:

$$f_o = \frac{1}{2\pi \sqrt{L_r C_r}}; \quad f_p = \frac{1}{2\pi \sqrt{(L_r + L_m)C_r}} \quad (2.10)$$

As observed in Fig.2.17, converter gain can be higher or lower than 1. The LLC resonant converter shows gain characteristics that are almost independent of the load when the switching frequency, $f_s$, is around the resonant frequency, $f_o$. This is a distinct advantage of LLC-type resonant converter over the conventional series resonant converter. Therefore, it is natural to operate the converter around the resonant frequency to minimize the switching frequency variation.

The DC characteristic of LLC resonant converter could be divided into ZVS region and ZCS region as shown in Fig.2.18 (a). With this characteristic, it could be placed at the resonant frequency of $f_o$ at high input, which is a resonant frequency of series resonant tank of $C_r$ and $L_r$. While input voltage drops, more gain can be achieved with lower switching frequency. With proper choose of resonant tank, the converter could operate within ZVS region for load and line variation. There are some interesting aspects of this DC characteristic. On the right side of $f_o$, this converter has same characteristic of SRC. On the left side of $f_o$, the image of PRC and SRC are fighting to be the dominant. At heavy
load, SRC will dominant. When load get lighter, characteristic of PRC will floating to the top. With these interesting characteristics, we could design the converter working at the resonant frequency of SRC to achieve high efficiency. Then we are able to operate the converter at lower than resonant frequency of SRC still get ZVS because of the characteristic of PRC will dominant in that frequency range. From above discussion, the DC characteristic of LLC resonant converter could be also divided into three regions, region 1 and region 2 and Region 3, according to different mode of operation as shown in Fig.2.18 (b).

![Fig.2.18 Operating Regions for LLC Resonant Converter](image1)

![Fig.2.19 DC Characteristic of LLC Resonant Converter](image2)

The operating range of the LLC resonant converter is limited by the peak gain (attainable maximum gain), which is indicated with "·" and connected as the boundary of ZVS and ZCS in Fig.2.18 (a). It should be noted that the peak gain does not occur at $f_0$.
nor $f_p$. The peak gain frequency where the peak gain is obtained exists between $f_p$ and $f_o$, as shown in Fig.2.18 (a). As Q decreases (as load decreases), the peak gain frequency moves to $f_p$ and higher peak gain is obtained. Meanwhile, as Q increases (as load increases), the peak gain frequency moves to $f_o$ and higher peak gain drops; thus, the full load condition should be the worst case for the resonant network design. And from Fig.2.19, it can be seen that the voltage gain is unity at resonant frequency, $f_o$, regardless of the Q or m variation.

The converter should be prevented from entering region 3 which is ZCS region, as illustrated with one gain curve in Fig.2.20.

![Fig.2.20 The switching frequency vs. the peak gain frequency](image)

Above the peak gain frequency also called here inductive region, the input impedance of the resonant tank is inductive and the input current of the resonant network ($i_p$) lags the voltage applied to the resonant tank ($V_d$). This permits the MOSFETs to turn on with zero voltage (ZVS). Meanwhile, the input impedance of the resonant tank becomes capacitive and the input current of the resonant network ($i_p$) leads the voltage applied to the resonant tank ($V_d$). below the peak gain frequency also called here capacitive region. When operating in capacitive region, the MOSFET body diode is reverse recovered during the switching transition, which results in severe noise. Another problem of entering into the capacitive region is that the output voltage easily becomes out of control since the slope of the gain is reversed.

Due to different operation mode of LLC resonant converter, its operation principles are quite complex. According to its switching frequency, LLC operation modes can be separated into above, below and equal to the resonant frequency.

2.3.1 Switching Frequency Equal to Resonant Frequency

For conventional resonant converters, such as SRC and PRC, it is desired to make the converter operate at the resonant frequency to maximize the circuit efficiency. However,
when these circuits operate on the left hand side of resonant frequency, circuits work under zero current switching. To ensure ZVS operation enough design margins has to be considered during design stage. Thus, the circuit would not be able to operate at the optimal operation point. For LLC resonant converter, ZVS switching can be achieved for the switching frequency either higher or lower than the resonant frequency. Thus, there is no such requirement for the design margin, and the circuit is able to operate at the resonant frequency while achieving optimal efficiency. For the circuit diagram shown in Fig.2.21 (a), operating principle at resonant frequency can be demonstrated in Fig.2.21 (b) and the corresponding topological modes can be summarized as in Fig.2.21 (c).

(a) Topology; (b) Key waveforms; (c) Topological modes

Fig.2.21 LLC converter operating at resonant frequency

At interval between $t_0$ and $t_1$, switch $S_1$ is conducting. In this period, the resonant tank current is larger than the magnetizing inductor current. According to the polarity of the transformer, secondary diodes $D_1$ and $D_4$ are conducting. Therefore, voltage applied to the transformer magnetizing inductance is the output voltage reflected to transformer primary side. Thus, magnetizing current linearly increases. During this period, the difference between the input voltage and output voltage is applied to the resonant tank, and resonant tank current is a sinusoidal waveform. At time $t_1$, resonant tank current reaches
magnetizing current and $S_1$ turns off. At interval $t_1$ and $t_2$, secondary diodes are off, because the resonant tank current is the same as magnetizing current and there is no current transferred to load. Due to the junction capacitors of $S_1$ and $S_2$, magnetizing current discharges the capacitors and help to achieve ZVS turn on of $S_2$. Both $S_1$ and $S_2$ are off. This period is known as the dead-time, which is used to allow enough time to achieve ZVS, as well as prevent shoot through of two switches. At time $t_2$, $S_2$ turn on with zero voltage switching. At interval between $t_2$ and $t_3$, the difference between the resonant tank current and the magnetizing inductor current is transferred to load. After $t_3$, $S_2$ is turn off and circuit operates into another half cycle. At resonant frequency, LLC resonant converter is able to achieve ZVS turn on for the primary side switches. Meanwhile, the switching turn-off current is maximum transformer magnetizing inductor current. By choosing a suitable magnetizing inductor, small turn-off loss can be realized. Moreover, secondary diodes turn off with low $di/dt$, which means smaller reverse recovery loss. Therefore, at resonant frequency, optimal performance of LLC resonant converter is expected. At resonant frequency, the series resonant tank impedance is equal to zero. Therefore, the input and output voltages are virtually connected together. Thus, the voltage gain at resonant frequency is equal to 1.

2.3.2 Switching Frequency Lower Than Resonant Frequency

When the switching frequency of LLC resonant converter is lower than the resonant frequency, magnetizing inductor participates in the circuit operation, which modifies the converter voltage gain characteristics. The equivalent circuit and key waveforms are shown in Fig.2.22 and the topological modes are shown in Fig.2.23.

![Diagram](image)

(a) Topology

(b) Key waveforms

Fig.2.22  LLC converter operating at lower resonant frequency

At interval between $t_0$ and $t_1$, switching $S_1$ and diodes $D_1$and $D_4$ are conducting, and the converter delivers energy to load. At time $t_2$, the resonant tank current resonates back
with a magnitude equal to the magnetizing current. After that, the magnetizing inductor begins to participate in the resonance. Since the resonant current is equal to magnetizing inductor current, the secondary diodes are turned off. At interval between $t_2$ and $t_3$, $S_1$ turns off and the magnetizing inductor transfers its stored energy to the resonant capacitor. Therefore, in this operation mode, the converter is able to boost the gain up. And the junction capacitors $C_{s1}$, $C_{s2}$ of the switches get fully charged and discharged before $t_3$. Then resonant tank transfers to the body diode of $S_2$. Thus $S_2$ achieves ZVS turn on. At interval $t_3$ and $t_4$, circuit enters the other half cycle.

Fig.2.23  Topological modes for LLC converter operating at lower resonant frequency

2.3.3 Switching Frequency Higher Than Resonant Frequency

When LLC resonant converter operates with switching frequency higher than the resonant frequency, the circuit operates as a SRC circuit. The equivalent circuit and key waveforms are shown in Fig.2.24 and the topological modes shown in Fig.2.25, respectively.

Fig.2.24  LLC converter operating at higher resonant frequency
At interval \( t_0 \) and \( t_1 \), switch \( S_1 \) is conducting and the circuit is transferring energy to load through diode \( D_1 \) and \( D_4 \). At time \( t_1 \), \( S_1 \) is turned off. Because the switching frequency is higher than resonant frequency, the resonant tank current is higher than the magnetizing current. At interval between \( t_1 \) and \( t_2 \), both \( S_1 \) and \( S_2 \) are off, the resonant tank current is charging and discharging the junction capacitors of primary side switches. At time \( t_2 \), voltage on junction capacitor of switch \( S_2 \) is discharged to zero. At interval between \( t_2 \) and \( t_3 \), the body diode of switch \( S_2 \) is turned on, the resonant tank current decreases quickly. At time \( t_3 \), the resonant tank current is equal to magnetizing current and diodes \( D_1 \) and \( D_4 \) turn off. At interval between \( t_3 \) and \( t_4 \), \( S_2 \) can be turned on with zero voltage switching and diodes \( D_2 \) and \( D_3 \) turn on and the circuit begins to transfer energy to load. In this operation mode, ZVS switching on primary side switches can be guaranteed due to the large turn off current. However, the large turn off current generates excessive turn-off loss on the primary side switches. Moreover, the secondary side diode turns off with large \( di/dt \), which can cause large reverse recovery on the diodes. Furthermore, the high \( di/dt \) turn off of the diodes cause extra voltage stress on the diode, which makes the circuit less reliable.

Fig.2.25 Topological modes for LLC converter operating at higher resonant frequency

From previous analysis, it can be seen that LLC resonant converter is able to achieve a larger gain below resonance operation, smaller above resonance operation or equal to 1 at resonance operation. When the circuit operates at resonant frequency, the converter voltage gain is equal to one, and circuit operates optimally. Operation below the resonant
frequency allows the soft commutation of the rectifier diodes in the secondary side, while the circulating current is relatively large. The circulating current increases more as the operation frequency moves downward from the resonant frequency. Below resonance operation also has a narrow frequency range with respect to the load variation since the frequency is limited below the resonant frequency even at the no-load condition. Operation above the resonant frequency allows the circulating current to be minimized, but the rectifier diodes are not softly commutated such that the reverse recovery loss might be severe. Above resonance operation has less conduction loss than the below resonance operation. However, operation at above the resonant frequency may cause too much frequency increase at light-load condition.

2.3.4 Design Considerations of LLC Resonant Converter

Since LLC resonant converter operates with switching frequency higher than resonant frequency, the circuit operates as a SRC circuit which cannot demonstrate the benefits of LLC resonant converter. In this case, ZVS switching on primary side switches can be guaranteed due to the large turn off current but it is very difficult to regulate the output at light load. Therefore, the LLC resonant converter is always designed to operate at region 2, which is below or equal to the resonant frequency but in ZVS region.

a. Determine Transformer Turns Ratio $n$

By choosing a suitable transformer turns-ratio, LLC resonant converter could operate with resonant frequency at normal condition and achieve high efficiency. Since at the resonant frequency, the converter voltage gain is equal to 1. To allow LLC converter operating with resonant frequency at normal condition, transformer turns-ratio in turn requires meeting the equation

$$ n = \frac{V_o}{V_{in}} $$

(2.11)

In this equation, $V_o$ is the desired output voltage, $V_{in}$ is the resonant tank input voltage at normal operation condition, which is equal to the bus voltage for full bridge structure and is equal to half of the bus voltage for half bridge structure.

b. ZVS Operation

In region 2, to achieve ZVS, there should be enough dead-time during which both switches $S_1$ and $S_2$ are off and duty cycle loss occurs because no power is delivered to load.
Fig.2.26 shows how to get enough dead-time to guarantee ZVS, where $C_{s1}$ and $C_{s2}$ is the equivalent output junction capacitance of $S_1$ and $S_2$, respectively.

![Fig.2.26 Dead-time requirement](image)

To realize ZVS, the turn-off current should be able to discharge and charge the junction capacitors during dead-time. It requires the turn-off current is smaller than the maximum current of the magnetizing inductor, thus,

$$
C_{s1} \frac{du_{ce1}}{dt} + C_{s2} \frac{du_{ce2}}{dt} = i_r \leq I_{Lm_{-max}} = \frac{nV_o T}{L_m 4}
$$

(2.12)

So the dead-time should meet

$$
t_{dead} \geq 8L_m \left( C_{s1} + C_{s1} \right) f_s
$$

(2.113)

c. **Determine Magnetizing Inductance**

Given the dead-time and switching frequency, to achieve ZVS it requires the magnetizing inductance to meet

$$
L_m \leq \frac{t_{dead} T_s}{8 \left( C_{s1} + C_{s1} \right)}
$$

(2.14)

Comparing with series resonant converter, LLC resonant largely reduces the magnetizing inductance. In this way, the magnetizing inductor can be used to realize soft switching for primary side switches. Furthermore, the magnetizing inductor participates into the resonance and modifies voltage gain characteristic. $L_m$ needs to be designed very properly. Switching loss is a controlled parameter. the turn-off current of primary switching is determined by the choice of resonant inductor $L_m$. A larger $L_m$ can produce less magnetizing current and less circulating energy, and RMS current can be minimized. But a larger $L_m$ can lead to smaller attainable maximum voltage gain, causing the output voltage not able to be regulated to meet the desired requirements.

d. **Determine the Ratio** $L_m / L_r$
While determining the maximum gain (Attainable Maximum Gain), the ratio \( m = \frac{L_m}{L_r} \) and \( Q \) need to be chosen properly.

From Fig.2.27, it shows that higher peak gain can be obtained by reducing \( Q \) or \( m \) values. With a given resonant frequency \( (f_r) \) and \( Q \) value, decreasing \( m \) means reducing the magnetizing inductance, which results in increasing circulating current. Accordingly, there is a trade-off between the available gain range and conduction loss. However, once magnetizing inductor is chosen, the relationship between \( L_n \) and \( Q \) has been fixed. From the definition of \( m \) and \( Q \), their product is

\[
m \cdot Q = \frac{L_m}{L_r} \cdot \frac{1}{R_o} \cdot \frac{1}{\sqrt{C_r}} = \frac{2\pi f_o}{R_o} L_m
\]

(2.15)

![Fig.2.27 Peak Gain vs Q for different m values](image)

Once converter specification is defined and switching frequency is chosen, the product of \( m \) and \( Q \) is only determined by the magnetizing inductor. Therefore, for the designed magnetizing inductor, the product of \( m \) and \( Q \) is set. Usually small \( m \) and large \( Q \) is preferred to get narrower \( f_s \) operation range which can be observed from Fig.2.19.

e. **Maximum Operation Gain**

The minimum switching frequency should be well limited above the peak gain frequency, which can be referred to Fig.2.28.

The available input voltage range of the LLC resonant converter is determined by the peak voltage gain. Thus, the resonant tank should be designed so that the gain curve has
an enough peak gain to cover the input voltage range. However, ZVS condition is lost below the peak gain point as depicted in Fig.2.28. Therefore, some margin is required when determining the maximum gain to guarantee stable ZVS operation during the load transient and start-up. Typically 10~20% of the maximum gain is used as a margin for practical design, as shown in Fig.2.28.

![Fig.2.28 Determining the Maximum Gain](image)

**2.3.5 Disadvantages of LLC Resonant Converter**

LLC is very attractive to overcome the issues of conventional circuits. With LLC resonant converter, performance at high input voltage could be optimized and the converter still could cover wide input voltage range. Fig.2.29 illustrates the key characteristics and formula of half-bridge LLC converter under ZVS conditions.

- Operation below the resonant frequency allows the soft commutation of the rectifier diodes in the secondary side, while the circulating current is relatively large. The circulating current increases more as the operation frequency moves downward from the resonant frequency.
- Larger m leads to wider frequency range. To get the frequency range narrower, m can be reduced. Decreasing m means reducing magnetizing inductance, $L_m$, which results in increased circulating current, thus, switching loss and conduction loss will increase. And larger $L_m$ means larger duty cycle loss because there is no power delivery during deadtime.
- Since the product of m and Q is fixed once $L_m$ and switching frequency are given, smaller m and larger Q is preferred to get narrower frequency range but results in smaller attainable peak gain. The problem with switching frequency lower than
resonant frequency is the conduction loss will increase as switching frequency drops.

(a) DC characteristics of half bridge LLC

(b) Peak Gain vs Q for different m values and key formula for half bridge LLC

Fig. 2.29 Key characteristics and formula of HB LLC converter

- For same specification, \( L_r \) and \( C_r \) can have different values, which will work. Although there is a limit on how small \( C_r \) can be in order to keep \( Q \) reasonable, \( C_r \) can be chosen larger, which makes smaller voltage stress on \( C_r \), but the impedance of the resonant tank will be small too. With smaller tank impedance, the short circuit current will be higher and higher switching frequency is needed to limit the output current, which will affect the short circuit performance.
CH3: Hybrid Resonant and PWM Converter

3.1 Motivations

From the previous chapter 2, it can be concluded that the phase shifted full bridge converter and LLC half-bridge resonant converter have their own merits and demerits, some of which are considered important for EV battery charger and summarized in Table 3.1, and none of the two are perfect.

<table>
<thead>
<tr>
<th>Control method</th>
<th>ZVS range</th>
<th>Circulating current</th>
<th>Constant Current and Voltage</th>
<th>Output diode voltage stress</th>
</tr>
</thead>
<tbody>
<tr>
<td>PS FB Fixed frequency</td>
<td>Limited range</td>
<td>High</td>
<td>Yes</td>
<td>High</td>
</tr>
<tr>
<td>LLC Variable frequency</td>
<td>Full range</td>
<td>Low</td>
<td>No</td>
<td>Low</td>
</tr>
</tbody>
</table>

Note: PS FB represents phase-shifted full bridge converter; LLC represents LLC converter.

In battery charger applications, ZVS is vitally important since the converter might be operating at absolutely no load for a long period of time. In this application, when the battery is charged, the load is absolutely zero, and the converter should be able to safely operate under the zero-load condition. From this view, the phase-shifted full bridge converter is very hard to meet this requirement. LLC seems a good candidate, but the variable frequency control makes it very complicated to handle all the conditions, and it is not easy to regulate the output current, which cannot meet the constant current charging requirement for EV battery charger.

So, what if they are hybrid together? Let LLC operate at fixed frequency very close to the resonant frequency, which is the best operating point to accomplish high efficiency. It can achieve ZVS from zero load to full load which is very vital in the battery charger system. It seems a good idea to make LLC solve soft switching problem and make the phase-shifted full bridge converter adjust the output voltage and the power levels.

3.2 Proposed Hybrid Resonant and PWM Converter

A novel Hybrid Resonant and PWM Converter in Fig.3.1 is presented to keep the advantages of high efficiency and small output inductance. The major features of the
hybrid resonant and PWM converter are as follows: 1) zero-voltage switching of MOSFETs in the leading-leg can be achieved from true zero to full load because of the parallel LLC resonant half-bridge configuration; 2) zero-current switching of IGBTs in the lagging-leg is realized in full line and load range with minimum circulating conduction loss due to effectively resetting of the parallel secondary-side constant DC voltage source; 3) duty cycle loss is negligible since the ZVS operation can be ensured even without the leakage inductance of the main transformer; 4) conduction loss during the output inductor freewheeling interval is significantly reduced because of no need for series diodes.

![Fig. 3.1 Hybrid Resonant and PWM Converter](image)

### 3.3 Operational Principles

Fig. 3.2 (a) show the circuit diagram of the Hybrid Resonant and PWM Converter which composed of two parts: 1) the resonant half-bridge circuit including two MOSFETs $S_1$ and $S_2$, loosely coupled transformer $TR_2$, resonant capacitor $C_3$, and the secondary rectifier $D_5$, $D_6$, and $C_1$, $C_2$; 2) the phase shifted full-bridge circuit including two MOSFETs $S_1$ and $S_2$ as leading-lag, two IGBTs as lagging-leg, tightly coupled transformer $TR_1$, the secondary rectifier $D_1$-$4$, and $D_7$, and the LC output filter. The topology operating principle can be explained by the gating sequence and associated key voltage and current waveforms shown in Fig.3.2 (b). Where $C_{s1}$, $C_{s2}$ are the equivalent capacitance of the MOSFETs $S_1$, $S_2$, respectively; $v_{rect}$ is voltage of the output inductor left-side point referred to the output ground; $V_o$ is the output voltage; $i_{pri1}$ and $i_{pri2}$ are the primary current of the transformer $TR_1$ and $TR_2$ respectively; $i_{Lm2}$ is the magnetizing current of the transformer $TR_2$; and the $v_{ds1}$ is the device $S_1$ drain-to-source voltage.
Fig. 3.2 Hybrid Resonant and PWM Converter

(a) Circuit configuration                                     (b) Key operating waveforms

Fig. 3.3 Topological modes of the proposed converter in half switching cycle
This Hybrid Resonant and PWM Converter combines the behavior of two different converter topologies: LLC half-bridge converter operating at the load-independent resonant frequency which makes the circuit operate at optimal condition to achieve maximum efficiency and the constant frequency phase shifted full-bridge converter which is used to regulate the output by means of the phase shift. There are six distinct operation modes for this topology in the PWM half cycle, as shown as Fig.3.3.

Mode \([t_0, t_1]\): At \(t_0\), Diode D7 turns off since the secondary current of transformer TR1 reaches the output inductor current. Switches S3 and S2 remain on. Suppose the leakage inductance of the main transformer is zero, that is \(L_{lk1} = 0\). Thus, the equivalent circuit at this interval is shown in Fig.3.4, as well as the key waveforms.

![Fig.3.4](image.png)

(a) (b) The equivalent circuit for Mode \([t_0, t_1]\); (c) the key waveforms

Clearly from Fig.3.4 (a), the reflected input voltage applies to the left-side of the output inductor called the rectified voltage, \(v_{\text{rect}}\), which can be expressed as

\[
v_{\text{rect}} = n_1 \cdot V_{\text{in}} \tag{3.1}
\]

where \(n_1\) is the secondary-to-primary turns ratio of TR1. \(v_{\text{rect}}\) is the rectified voltage and \(V_{\text{in}}\) is input voltage shown in Fig.3.2(b). The primary current of the main transformer reaches the reflected current of the output inductor, \(L_{o}\), and increases with the slope as

\[
\frac{di_{\text{pri}}}{dt} = \frac{(n_1 V_{\text{in}} - V_o) / (L_o / n_1)} \tag{3.2}
\]

According to half bridge LLC characteristics, the \(v_{\text{sec}}\) shown in from Fig.3.4 (b) can be expressed as
\[ v_{\text{sec}2} = n_2 \cdot \left( \frac{1}{2} V_{\text{in}} \right) \] (3.3)

Suppose output capacitors, \( C_1 \) and \( C_2 \), are large enough. Thus, the primary side of Fig.3.4 (b) can be simplified as Fig.3.6 as follows.

![Fig.3.5 The simplified circuit for the primary side of Fig.3.4 (b)](image)

The magnetizing current \( i_{Lm2} \) can be simplified as a triangle wave with a constant upward slope as follows.

\[ \frac{di_{Lm2}}{dt} = \frac{V_{\text{in}}/2}{L_m} \] (3.4)

where \( n_2 \) are the secondary-to-primary turns ratio \( TR_2 \). Thus,

\[ i_{Lm2}(t) = \left[ i_{Lm2}(t_0) + \frac{V_{\text{in}}/2}{L_m} (t - t_0) \right] \] (3.5)

\( i_{Lm2}(t_0) \) is the current flowing the resonant capacitor \( L_{m2} \) at \( t_0 \).

Since the circuit operates at resonant frequency, where the voltage gain is constant, a little bit higher than unity, which is independent of load and ratio of \( m = L_m / L_{lk} \), \( L_m \) is the transformer magnetizing inductance and \( L_{lk} \) is the transformer leakage inductance, \( L_{m2} \) can be relatively large as needed. Suppose output capacitors, \( C_1 \) and \( C_2 \), are large enough. Then the secondary side of Fig.4 (b) can be simplified as Fig.3.6 as follows.

![Fig.3. 6 The simplified circuit for the secondary side of Fig.3.5 (b)](image)
Suppose the voltage across the resonant capacitor $C_3$ at $t_0$ is $V_{c3}(t_0)$, the $i_x$ can be derived as follows by means of the Laplace model of the circuit in Fig.3.5.

$$i_x = \frac{[V_{in} / 2 - V_{c3}(t_0)]}{Z_o} \sin \left[ \omega_r (t - t_1) \right]$$

(3.6)

Thus, the auxiliary transformer primary current, $i_{pri2}$, which increases with resonance between the leakage inductor, $L_{lk2}$, and the resonant capacitor, $C_3$, is given by

$$i_{pri2} = \frac{[V_{in} / 2 - V_{c3}(t_0)]}{Z_o} \sin \left[ \omega_r (t - t_1) \right] + i_{Lm2}(t)$$

(3.7)

where $Z_o = \sqrt{L_{lk2} / C_3}$ and $\omega_r = \frac{1}{\sqrt{L_{lk2} C_3}}$, $V_{c3}(t_0)$ is the voltage across the resonant capacitor $C_3$ at $t_0$.

Mode $[t_1, t_2]$: At $t_1$, $S_2$ is turned off by the PWM command, and the sum of two transformers primary current will charge and discharge the MOSFET capacitors $C_{s2}$ and $C_{s1}$, respectively. At $t_2$, $C_{s1}$ and $C_{s2}$ can be fully discharged and charged under any output current condition due to load-independent magnetizing current $i_{Lm2}$. With $C_{s1}$ being discharged, switch voltage $v_{ds1}$ starts falling. Under zero-load condition which the worse case for this circuit, the main transformer (TR1) primary current is zero, $i_{pri1} = 0$ and the auxiliary transformer (TR2) primary current, $i_{pri2}$ equivalent to $i_{Lm2}$, is designed to have the ability to fully charge and discharge the output capacitors of the switches to guarantee the devices under ZVS condition.

Fig.3.7 The equivalent circuit under zero load condition (worst case)

Fig.3.7 shows how the circuit guarantees the devices under ZVS condition only if the $L_m$ is designed well to guarantee the current, $i_{Lm2}$, is big enough to fully charge and discharge the output capacitors of the switches.
In this case, $L_{m2}$ is resonant with $C_{s1}/C_{s2}$ and the maximum resonant time is a quarter of the switching period.

$$v_{ds1} = V_{in} \cos \left[ \omega_{m2} \left(t - t_1\right) \right]$$  \hspace{1cm} (3.8)

where $\omega_{m2} = 1/\sqrt{L_{m2} (C_{s1} + C_{s2})}$

The rectified voltage, $v_{rect}$, starts falling to the valley as

$$v_{rect} = n_2 \cdot V_{in}$$  \hspace{1cm} (3.9)

Mode $[t_2, t_3]$: The body diode of $S_1$ is on and switch $S_1$ voltage $v_{ds1}$ keeps zero. The TR1 primary current starts to be resetting effectively by the parallel secondary-side DC voltage source produced by LLC half-bridge converter. The equivalent circuit at this interval is shown in Fig.3.8, as well as the key zoomed waveforms.

Fig.3.8  (a), (b)The equivalent circuit for Mode $[t_2, t_3]$; (c) zoomed key waveforms

From Fig.3.8, it can be seen that the primary current of the main transformer decreases with the slope as follows.

$$- \frac{di_{pri1}}{dt} = \frac{n_2}{n_1} \frac{V_{in}}{L_{lk1}}$$  \hspace{1cm} (3.10)

Since $L_{lk1}$ can be designed very small because there is no need to consider the tradeoff resulting from $L_{lk1}$ in this proposed circuit, the resetting time can be very short.

And the magnetizing current $i_{Lm2}$ starts to decrease with a constant slope as

$$- \frac{di_{Lm2}}{dt} = \frac{V_{in}}{2L_m}$$  \hspace{1cm} (3.11)

Mode $[t_3, t_4]$: At $t_3$, $S_1$ can be turned on under zero-voltage condition by PWM
command. The gate of $S_3$ remains on but no current flowing through $S_3$.

Mode $[t_4, t_5]$: At $t_4$, the switch $S_3$ is turned off by PWM command under zero current condition since the transformer $TR_1$ current keeps zero. During the intervals $[t_3, t_4]$ and $[t_4, t_5]$, the energy is still being transferred from input to the output even when the output inductor is freewheeling because the LLC half-bridge is working.

Mode $[t_5, t_6]$: At $t_5$, IGBT $S_4$ is turned on. The $TR_1$ secondary current value starts increasing until it arrives at current level of the output inductor. The equivalent circuit at this interval is shown in Fig.3.9, as well as the key zoomed waveforms.

From Fig.3.9, it can be seen that the slope of the $TR_1$ primary current can be simply expressed as

$$\frac{di_{pri1}}{dt} = \frac{n_1 - n_2}{n_1} \frac{V_{in}}{L_{lk1}} \quad (3.12)$$

where $n_1$ and $n_2$ are the secondary-to-primary turns ratio of $TR_1$ and $TR_2$ respectively; $L_{lk1}$ is the primary leakage inductance of $TR_1$ and $i_{pri1}$ is the primary current of the main transformer $TR_1$. Duty cycle loss occurs during this interval. This proposed circuit can have the potential to get very small duty cycle loss because the leakage inductance of the main transformer is independent of the zero-voltage-switching and can be minimized.

### 3.4 Design Considerations

#### 3.4.1 Transformers Turns Ratio
According to the voltage-second balance across the output inductor and the secondary rectifier voltage waveform shown in Fig. 3.10, we can obtain

\[ (n_1 V_{in} - V_o) D_{eff} = (V_o - n_2 V_{in}) (1 - D_{eff}) \]  \hspace{1cm} (3.13)

where \( D_{eff} \) is the effective duty cycle.

Then, the steady state voltage gain in continuous conduction mode can be described as

\[ \frac{V_o}{V_{in}} = D_{eff} (n_1 - n_2) + n_2 \]  \hspace{1cm} (3.14)

where \( n_2 < n_1 \). This equation shows that the voltage gain varies between \( n_1 \) (when \( D=1 \)) and \( n_2 \) (when \( D=0 \)) as illustrated in Fig.3.11.

Therefore, the secondary-to-primary turns ratio \( n_1 \) of TR1 and \( n_2 \) of TR2 should be chosen as

\[ n_1 = \frac{V_{o,\max}}{V_{in,\min}} \]  \hspace{1cm} (3.15)

\[ n_2 = \frac{V_{o,\min}}{V_{in,\max}} \]  \hspace{1cm} (3.16)

### 3.4.2 ZVS under True Zero Load condition

It can be seen from topology mode \([t_1, t_2]\) shown in Fig. 3.3 that the half-bridge and full-bridge are in parallel during the leading leg transition. The ZVS energy and time conditions can be satisfied from true zero to full load because the peak value of magnetizing current in the auxiliary transformer is independent of the output voltage and output current as follows.

\[ I_{L_{m2 \_ peak}} = \frac{V_{in}/2}{4 L_{m2}} \]  \hspace{1cm} (3.17)
where $I_{Lm2_{\text{peak}}}$ is the peak magnetizing current of the auxiliary transformer TR$_2$, $L_{m2}$ is the magnetizing inductance of the auxiliary transformer TR$_2$, $f_s$ is switching frequency. Equation (17) shows that the magnetizing inductance, $L_{m2}$, should be designed well to get lower conduction loss under ZVS condition.

To guarantee ZVS under no load condition, the turn-off current should be able to discharge and charge the junction capacitors during dead-time as illustrated in Fig.3.12.

![Fig. 3.12 ZVS condition under no load](image)

It requires the turn-off current is smaller than the maximum current of the magnetizing inductor, thus,

$$C_{s1} \frac{dv_{ds1}}{dt} + C_{s2} \frac{dv_{ds2}}{dt} = i_{\text{off}} \leq I_{Lm2_{\text{peak}}}(3.18)$$

So the dead-time should meet

$$t_{\text{dead}} \geq \frac{8L_{m2}(C_{s1} + C_{s2})f_s}{(3.19)}$$

where $t_{\text{dead}}$ is dead time.

Equations (3.17) and (3.19) show that magnetizing inductance selection $L_{m2}$ is a trade-off between the minimum dead time limitation for ZVS under no load condition and the current stress of MOSFETs.

### 3.4.4 Duty Cycle Loss

From Fig.3.13 and the topology mode $[t_5, t_6]$ shown in Fig.3.3, the duty cycle loss seen by the output inductor can be derived as

$$\Delta D_{\text{loss}} = \frac{2n_1^2L_{lk1}I_o f_s}{(n_1 - n_2)V_{in}}$$

(3.20)

where $I_o$ is the output current. It is clear from the equation (3.20) that if $L_{lk1}$ is close to zero, the duty cycle loss is close to zero. Here, $L_{lk1}$ can be designed very small because the zero-voltage-switching range is independent of the value of $L_{lk1}$ in this circuit.
3.4.5 Transformer Magnetizing and Leakage Inductance

The fundamental purpose of any magnetic core is to provide an easy path for flux in order to facilitate flux linkage, or coupling, between two or more magnetic elements. It serves as a "magnetic bus bar" to connect a magnetic source to a magnetic "load". In a true transformer application, the magnetic source is the primary winding -ampere-turns and volts/turn. The magnetic "load" is the secondary winding (or windings). The flux through the core links the windings to each other. It also enables electrical isolation between windings, and enables adaptation to different voltage levels by adjusting the turns ratio. Ideally, a transformer stores no energy, but transfers energy immediately from input to output. In a practical transformer, undesired stored energy does occur in parasitic leakage inductances (outside the core), and magnetizing inductance (within the core). Energy storage in a transformer core is an undesired parasitic element. With a high permeability core material, energy storage is minimal. Magnetizing inductance is maximized by using a gapless, high permeability core material.

a. Magnetizing and Leakage Inductance of Main Transformer TR1

The larger magnetizing inductance is, the less energy storage in a transformer core is and the less circulating current is, thus, the main transformer magnetizing is better designed very large. In this circuit, zero-voltage-switching range is independent of the value of $L_{ikj}$. Thus, the optimal is making the leakage inductance very small. How to get it desired? The magnetizing inductance and leakage inductance of the main transformer can be designed naturally. The magnetizing inductance can be designed well by using a gapless, high permeability core material to get it as large as possible. The leakage inductance can be reduced by extensive interleaving of primary and secondary windings.
as shown in Fig. 3.14, where MMF is magneto- motive force or Ampere turns and $M$ is number of primary–secondary intersections. The main transformer leakage inductance, $L_{lk1}$, can be expressed analytically as follows.

$$L_{lk1} = \mu_o \frac{N^2 l_w}{M^2 b_w} \left( \frac{1}{3} \sum_{P=1}^{M} h_p + \sum_{\Delta=1}^{M} h_\Delta \right)$$

(3.21)

If $h_\Delta \ll h_p$, transformer leakage inductance is approximately

$$L_{lk1} = \mu_o \frac{l_w h_w N^2}{3b_w M^2}$$

(3.22)

where $h_\Delta$ is height of primary-secondary intersection; $h_p$ is height of $P_{th}$ winding portion; $h_w$ is total height of transformer winding; $l_w$ is mean turn length; $b_w$ is breadth of winding; $M$ is number of primary–secondary intersections; $N$ is number of winding turns; $\mu_0$ is permeability of free space. From (3.21) and (3.22), it is clear that the extensive interleaving of primary and secondary windings, as required in high-power low-voltage transformers, will lead to very small stored energy in transformer leakage inductance. Furthermore, it becomes clear that, with leakage inductance being proportional to the squared number of turns $N^2$, the few primary turns of low voltage high-power transformers have inherently extremely small leakage inductance.

Fig. 3.14 Alternative transformer winding configurations
b. Magnetizing and Leakage inductance of Auxiliary Transformer TR2

First, let us go over the design considerations of LLC at resonant frequency which is the best operating point to get highest efficiency. From Fig.3.15, it can be seen that the voltage gain of LLC keeps constant while operating at resonant frequency regardless the variations of $m$ or $Q$. Thus the part of LLC design becomes very easy. The LLC design at resonant frequency is simplified a lot because only the best operating point is considered, thus there is no trade-off to be considered during design.

![Fig.3.15 DC characteristics of half bridge LLC](image)

- At full load, a reasonable $Q$ must be set to make sure there is some margin to guarantee stable ZVS operation since the switching frequency is not exactly the same as the resonant frequency, practically a little bit lower than resonant frequency.

- For $L_m$, using this formula $L_m \leq \frac{i_{\text{dead}} T_s}{8 (C_{s1} + C_{s1})}$ to guarantee ZVS realization, $L_m$ can be larger under this condition in the hybrid converter because there is no need to consider frequency range where the converter operates at fixed frequency.

- Since the voltage gain is independent of $m$ ($m=L_m/L_r$), the ratio of magnetizing inductance and leakage inductance of the LLC transformer, $L_r$ is only limited by $Q$ and $f_r$.

Since this circuit operates at the resonant frequency, there is no worry about the attainable peak voltage gain of the circuit to get the desired regulated output voltage, which is controlled by the phase-shifted full bridge converter. Because the voltage gain of LLC converter is independent of $m$ ($m=L_m/L_r$) at resonant frequency as shown in Fig.3.15, the
magnetizing inductance and leakage inductance of the auxiliary transformer can also be designed naturally, which is much easier compared to the pure LLC converter.

The magnetizing inductance can be obtained by adjusting the gap which is physically in series with the core under the only ZVS requirement of \( L_{m2} \leq \frac{t_{\text{dead}}}{8(C_{s1} + C_{s2})f_r} \). Since the leakage inductance is resonant with the resonant capacitor to set the operating frequency, there is no need to use interleaving windings to get the leakage inductance reduced. The leakage inductance can be naturally obtained and precisely controlled by the practical insulation distance between the primary and the secondary windings. When the ETD type core with the simplest winding structure without interleaving is employed, the leakage inductance is calculated by

\[
L_{lk2} = \frac{4\pi N_{pri}^2 l}{H} \left( \frac{h_1 + h_3}{3} + h_2 \right) \times 10^{-9}
\]

(3.23)

where \( l \) is the mean length of turn for whole coil, \( H \) is the total winding height, \( h_1 \) is the primary winding width, \( h_2 \) is the insulation distance, and \( h_3 \) is the secondary winding width. Note that all dimensions are in centimeters and \( L_{lk2} \) is in henries.

### 3.4.6 Resonant Capacitance

From Fig.3.16 it can be seen that the voltage gain of LLC half-bridge converter is independent of the load when it operates at the resonant frequency \( f_r \), the resonant capacitor can be found to be

\[
C_3 = \frac{1}{\left(\frac{2\pi f_r}{L_{lk2}}\right)} \left( \frac{L_{lk2}}{f_r} \right)
\]

(3.24)

![Fig.3.16 LLC converter voltage gain vs. normalized frequency](image)

In this converter, the phase-shifted full bridge ZVZCS converter is responsible to get the expected output voltage of the converter. The LLC half bridge converter is to guarantee the leading leg, \( S_1 \) and \( S_2 \), to operate at ZVS from true zero load to full load. The operating
The frequency is given constant at the optimized frequency according to the LLC half bridge converter, for example, 46.7 kHz in the following experimental prototype next chapter. Theoretically, this hybrid converter can integrate the advantages of the LLC resonant converter and phase-shifted PWM full bridge converter.

3.4.7 Output Inductance

Fig. 3.17 (a) is the rectified voltage waveform of the conventional full bridge converter. The peak-to-peak current ripple can be expressed as

$$\Delta i_{pk-pk}(V_o) = \frac{T_s}{n_1 L_o} (n_1 - \frac{V_o}{V_{in}}) V_o$$  \hspace{1cm} (3.25)$$

Fig. 3.17 (b) is the rectified voltage waveform of the proposed converter. The peak-to-peak current ripple can be expressed as

$$\Delta i_{pk-pk}(V_o) = \frac{V_{in} T_s}{(n_1 - n_2) L_o} (n_1 - \frac{V_o}{V_{in}})(\frac{V_o}{V_{in}} - n_2)$$  \hspace{1cm} (3.26)$$

By solving the equations (25) and (26), it yields

$$\frac{\Delta i_{2, pk-pk, max}}{\Delta i_{1, pk-pk, max}} = 1 - \frac{n_2}{n_1}$$  \hspace{1cm} (3.27)$$

where \(n_2 < n_1\). And given \(n_2/n_1 = 4:9\), the relationship of the normalized output voltage and normalized output inductor peak-to-peak current is shown in Fig. 3.18.

Fig.3.18 Normalized peak-to-peak output inductor current vs. normalized output voltage.
It can be seen from the equation (3.27) and Fig.3.18 that the output inductor current ripple in the proposed converter can be reduced by $n_2/n_1$ compared to the conventional full bridge, which means the inductance can be reduced by $n_2/n_1$ compared to the conventional full bridge under the same current ripple condition.

### 3.5 Simulation Circuit and Simulation Results

Based on the previous analysis, the circuit is designed and the simulation circuit is shown in Fig.3.19. Correspondingly, the simulation results are given at full load (worst case for IGBTs ZCS condition) and no load (worst case for MOSFETs ZVS condition) shown in Figs.3.20~24. And the specifications are given in table 3.1.

![Simulation Circuit Diagram](image)

Fig.3.19 Power stage of the simulation circuit

**Table 3.1: Simulation specifications**

<table>
<thead>
<tr>
<th></th>
<th>Full load (worst case for IGBT ZCS)</th>
<th>No load (worst case for MOSFET ZVS)</th>
</tr>
</thead>
<tbody>
<tr>
<td><strong>Input Voltage</strong></td>
<td>390V</td>
<td>390V</td>
</tr>
<tr>
<td><strong>Output Voltage</strong></td>
<td>385V</td>
<td>385V</td>
</tr>
<tr>
<td><strong>Output Power</strong></td>
<td>6.6kW</td>
<td>0W</td>
</tr>
<tr>
<td><strong>Switching freq.</strong></td>
<td>46.7kHz</td>
<td>46.7kHz</td>
</tr>
</tbody>
</table>
From Fig.3.20, it can be seen that ZCS operation of the main device IGBTs is verified by the simulation waveforms of the IGBT (S₄) voltage $V_{ce4}$, device current $i_{cd}$, and gate voltage $G₄$. Before the gate is turned off, the device current $i_{cd}$ is zero, so the IGBT operates at zero-current switching condition in the worst case of the maximum output power.

Fig.3.20 IGBT waveforms of the voltage, current, and its gate at full load

Fig.3.21 MOSFET waveforms of the voltage, current, gate and output current at full load
It can be seen from Figs. 3.21, 3.22 that the main switches of MOSFETs demonstrate ZVS operation with load current adaptability. Fig. 3.21 shows the device MOSFET, S2, drain-to-source voltage $v_{ds2}$ and its gating signal $G_2$ at the full load condition and Fig. 3.22 shows $v_{ds2}$ and $G_2$ at no load current condition. By observing that $v_{ds2}$ drops to zero before $G_2$ turns ON at different output current levels, both figures clearly indicate that ZVS is achieved from true zero to full load.

Fig. 3.23 Full-bridge diode D1 waveforms of voltage, current and its associated transformer secondary current at full load
The fast reset of the circulating current of the transformer TR₁ during the output inductor freewheeling interval is illustrated in Fig. 3.23. The secondary side current \( i_{\text{sec1}} \) of transformer TR₁ drops to zero in 0.8\( \mu \text{s} \) with the low leakage inductance because that ZVS of MOSFET can be achieved in the converter even while the leakage inductance is zero. It also can be seen that full-bridge diode D₁ is turned off under relatively low voltage without severe reverse current.

![Waveform diagram](image)

**Fig. 3.24 Half-bridge diode D₅ waveforms of voltage and its associated transformer secondary current at full load**

Fig. 3.24 shows the waveforms of the half-bridge diode ZCS turn-on and turn-off in the worst case of full load condition. The well-clamped voltage stress and ZCS operation of the half-bridge diode imply that the diode voltage stress is low and the low-voltage drop diode can be utilized to further improve the efficiency.

### 3.6 Performance Analysis of Hybrid Resonant and PWM Converter

As mentioned previously, this converter is able to achieve very high efficiency. In order to obtain high efficiency, proper topology selection is critical but understand the sources of system loss is also crucial. Many sources of loss exist in a system. First, primary sources of loss will be considered. Some primary sources of loss are easy to model while others may be more difficult. Primary sources of loss include the following.

- Active device conduction loss
- Diode conduction loss
• Switching loss
• Transformer core loss
• Transformer winding loss
• Inductor loss

Both active device conduction loss and diode conduction losses are fairly easy to estimate as long as circuit operation is properly understood. Complications arise when temperature effects are taken into account. Losses increase for MOSFETs and IGBTs at higher temperatures and losses decrease for diodes at higher temperatures. A rough temperature prediction can be used to improve the models. Switching loss may be difficult to estimate accurately due to various parasitics. Package and PCB parasitic inductances may alter switching times and switching waveforms. Both core and dc transformer winding losses are relatively easy to estimate, although thermal effects can create inaccuracies.

In addition to the above mentioned primary sources of loss, several parasitic sources of loss exist. The parasitic losses include but are not limited to the following:
• Snubber loss
• Capacitor ESR loss
• Body diode conduction loss
• Skin effect
• Proximity effect
• Contact and termination loss
• Switching losses due to loss of soft switching condition
• Various losses due to temperature variation

The parasitic losses mentioned above are particularly difficult to characterize. The losses due to skin effect and proximity effect are very difficult to model. Skin effect losses can be prevented for the most part by utilizing copper windings which are thin enough to ensure that sufficient surface area is available. Proximity effects are difficult to predict as the effect is heavily dependent on how the transformer is wound. Contact and termination losses are also difficult to model and predict. The resistance of a contact may be very small but under high current conditions, the loss can be substantial. Switching losses due to non-full ZVS condition is once again, difficult to predict. Partial ZVS conditions are
possible as shown previously. Therefore, the actual loss is very difficult to model. Finally, the system suffers from losses due to temperature variations. It is difficult to know exact junction temperatures of devices or core temperatures. The temperature is also dependant on cooling and environmental factors as well. Temperature effects are partially considered in order to form better models.

3.6.1 Main Components in This Circuit

The prototype converter has the following specifications: input voltage \( V_{in} = 380V \sim 400V \); output voltage \( V_o = 250V \sim 450V \); Maximum output current \( I_{o,max} = 15A \); switching frequency \( f_s = 46.7kHz \). And the main components are tabulated as follows.

<table>
<thead>
<tr>
<th>Table 3.2: main components used in the circuit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Designator</td>
</tr>
<tr>
<td>------------</td>
</tr>
<tr>
<td>MOSFETs</td>
</tr>
<tr>
<td>IGBTs</td>
</tr>
<tr>
<td>Diodes</td>
</tr>
<tr>
<td>Diodes</td>
</tr>
<tr>
<td>Diodes</td>
</tr>
</tbody>
</table>

Transformers and inductor information:

<table>
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<tr>
<th>Transformer</th>
<th>Core: Ferrite EE80</th>
<th>Pri. wire #: 12</th>
<th>Sec. wire#: 12</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>TR(_1)</td>
<td></td>
<td></td>
<td></td>
<td>Main transformer</td>
</tr>
<tr>
<td>TR(_2)</td>
<td></td>
<td></td>
<td></td>
<td>Auxiliary transformer</td>
</tr>
<tr>
<td>Inductor</td>
<td>Core: C058195A2(High flux)</td>
<td>Wire#:11</td>
<td>(Litz wire)</td>
<td>Output inductor</td>
</tr>
</tbody>
</table>

3.6.2 MOSFETs and IGBTs Conduction Loss Analysis

According datasheet, the power losses of MOSFETs and IGBTs can be calculated [68], [69].

(a) MOSFETs Conduction Loss Analysis
Conduction losses in power MOSFET can be calculated using an MOSFET-approximation with the drain source on-state resistance ($R_{DS(on)}$):

$$v_{DS}(i_D) = R_{DS(on)}(i_D) \cdot i_D$$  \hspace{1cm} (3.28)

where $v_{DS}$ and $i_D$ are drain-source voltage and the drain current, respectively.

The typical $R_{DS(on)}$ can be read from the data-sheet diagram, as shown in Fig. 3.25(a), where $I_D$ is the MOSFET on-state current as defined by the application. Therefore, power losses over the switching cycle gives an average value of the MOSFET conduction losses:

$$P_{CM} = R_{DS(on)} \cdot I_{D_{rms}}^2$$  \hspace{1cm} (3.29)

where $I_{D_{rms}}$ is the rms value of the MOSFET on-state current.

![Diagram](image)

(a) $R_{DS(on)}$ vs. drain current  \hspace{1cm} (b) $T_J$ vs. $R_{DS(on)}$

Fig. 3.25 Reading data from data sheet

The procedure for $R_{DS(on)}$ determination, shown in Fig. 3.25 (b), refers to the $R_{DS(on)}$ typical values. While this procedure should be satisfying for the majority of applications, the $R_{DS(on)}$ value can be calculated by taking into account the temperature and production variations. It can be done using following equation:

$$R_{DS(on)}(T_J) = R_{DS(on)_{max}}(25^\circ C) \cdot (1 + \frac{\alpha}{100})^{T_J - 25^\circ C}$$  \hspace{1cm} (3.30)

Where $T_J$ is the junction temperature and $R_{DS(on)_{max}}(25^\circ C)$ is the maximum value of $R_{DS(on)}$ at $25^\circ C$, which can be read from the product summary table in the data-sheet as shown in the Fig. 3.26.
The temperature coefficient $\alpha$ can be calculated in the following manner: Two sets of values $(T_{j1}, R_{DS(on)}1)$ and $(T_{j2}, R_{DS(on)}2)$ can be read from the data sheet as shown in Fig.3.27. These values can be used to determine $\alpha$ in equation (3.29).

The conduction losses of the anti-parallel diode can be estimated using a diode approximation with a series connection of DC voltage source ($v_{D0}$) representing diode on-state zero-current voltage and a diode on-state resistance ($R_D$), $v_D$ being the voltage across the diode and $i_F$ the current through the diode:

$$v_D(i_F) = v_{D0} + R_D \cdot i_F$$  \hspace{1cm} (3.31)

These parameters can be read from the diagrams in the MOSFET datasheet as shown in Fig.3.27. In order to take the parameter variation into account, and thus to have a conservative calculation, the $V_{D0}$ value read from the diagram have to be scaled with $(V_{D_{max}}/V_{Dtyp})$. Those exact values can be read from the datasheet tables, but for an engineering calculation a typical safety margin value of (10%-20%) can also be used.

If the average diode current is $I_{Fav}$, and the rms diode current is $I_{Frms}$, the average diode conduction losses across the switching period ($T_{sw} = 1/f_{sw}$) are:

$$P_{CD} = V_{D0}I_{Fav} + R_DI_{Frms}^2$$  \hspace{1cm} (3.32)
(b) IGBTs Conduction Loss Analysis

IGBT Conduction losses can be calculated using an IGBT approximation with a series connection of DC voltage source \( V_{CE0} \) representing IGBT on-state zero-current collector-emitter voltage and a collector-emitter on-state resistance \( r_C \):

\[
v_{CE}(i_C) = V_{CE0} + r_C \cdot i_C
\]  

(3.33)

The same approximation can be used for the anti-parallel diode, giving:

\[
v_D(i_D) = V_{D0} + r_D \cdot i_D
\]  

(3.34)

These important parameters can be read directly from the IGBT Datasheet (see Fig.3.28 (a) for the IGBT and Fig.3.28 (b) for the Diode). In order to take the parameter variation into account, and thus to have a conservative calculation, the \( V_{CE0} \) and \( V_{D0} \) values read from the diagram have to be scaled with \( \frac{V_{CE\text{max}}}{V_{CE0}} \) or \( \frac{V_{D\text{max}}}{V_{D0}} \)

values. Those exact values can be read from the datasheet tables, but for an engineering calculation a typical safety margin value of (1.1-1.2) can be used.

If the average IGBT current value is \( I_{Cav} \), and the rms value of IGBT current is \( I_{Crms} \), then the average losses can be expressed as:

\[
P_{CT} = V_{CE0} I_{Cav} + r_C I_{Crms}^2
\]  

If the average diode current is \( I_{Dav} \), and the rms diode current is \( I_{Drms} \), the average diode conduction losses across the switching period \( T_{sw} = \frac{1}{f_{sw}} \) are:

\[
P_{CD} = V_{D0} I_{Dav} + r_D I_{Drms}^2
\]  

(3.36)

Fig. 3.28 Reading data from datasheet
3.6.3 Diode Conduction Loss Analysis

In addition to MOSFETs and IGBTs conduction losses, there are diode conduction losses on the secondary side.

When the forward current $I_{\text{max}}$ is lower than $3 \cdot I_{\text{Fav}}$, similar to the anti-parallel diode loss calculation of the active device, the diode conduction loss can be calculated as

$$P_{\text{CD}} = V_F \cdot I_{\text{Fav}} + R_{\text{ak}} \cdot (I_{\text{Fms}})^2$$  \hspace{1cm} (3.37)

where $V_F$ is Diode fixed voltage drop under zero current condition; $I_{\text{Fav}}$ is average forward current in the diode; $I_{\text{Fms}}$ is RMS forward current in the diode; $R_{\text{ak}}$ Diode on-drop resistance.

When the forward current $I_{\text{max}}$ is higher than $3 \cdot I_{\text{Fav}}$, diode on-drop resistance, $R_{\text{ak}}$, becomes very pessimistic. The diode conduction loss can be calculated as

$$P_{\text{CD}} = V_{\text{FM}}(I_M) \cdot I_{\text{Fav}}$$  \hspace{1cm} (3.38)

where $V_{\text{FM}}(I_M)$ is the $V_{\text{FM}}$ value when $I_{\text{FM}} = I_M$; $I_{\text{Fav}}$ is average forward current in the diode.

3.6.4 MOSFET and IGBT Switching Loss Analysis

Switching loss is also a common source of loss in switching converters. Loss must be calculated for both turn-on and turn-off conditions to find the total switching loss. During commutation, voltage and current can be high as each crosses over the other. The switching energy loss, $E_{\text{sw}}$, is the integration of the $V \cdot I$ product during the commutation state.

$$E_{\text{sw}} = \int_{t_{i_{\text{on}}}}^{t_{i_{\text{off}}}} v_{\text{sw}}(t) i_{\text{sw}}(t) dt = E_{\text{on}} + E_{\text{off}} = \int_{t_{i_{\text{on}}}}^{t_{i_{\text{on}}}} v_{\text{sw}}(t) i_{\text{sw}}(t) dt + \int_{t_{i_{\text{on}}}}^{t_{i_{\text{off}}}} v_{\text{sw}}(t) i_{\text{sw}}(t) dt$$  \hspace{1cm} (3.39)

where $t_{i_{\text{on}}}$ is used for the unambiguous definition of integration limits for the determination turn-on switching losses; $t_{i_{\text{off}}}$ is used for the unambiguous definition of integration limits for the determination turn-off switching losses; $E_{\text{on}}$ is turn-on energy loss; $E_{\text{off}}$ is turn-off energy loss.
If soft switching is achieved, the switching loss for that particular device can be reduced significantly. Under ZVS or Zero Current Switching (ZCS) conditions, the switching loss can be considered zero.

Then the average switching loss can be expressed as

\[ P_{sw} = \frac{E_{sw}}{T_{sw}} = f_{sw} E_{sw} \quad (3.40) \]

The switching times are defined as follows:

- \( t_{d(on)} \) is turn-on delay time; \( t_{d(off)} \) is turn-off delay time; \( t_r \) is rise time; \( t_f \) is fall time; and \( t_{on} = t_{d(on)} + t_r \) is turn-on time; \( t_{off} = t_{d(off)} + t_f \) is turn-off time.

The values for \( t_{off} \) and \( t_{on} \) should ideally be measured. Sometimes, measurement may be difficult. Typically, the device manufacturer will provide some typical values for \( t_{off} \) and \( t_{on} \) and values for \( E_{off} \) and \( E_{on} \) maybe provided as well. Unfortunately, the values for \( t_{off}, t_{on}, \) and \( E_{off}, \) and \( E_{on} \) are dependent on many factors including temperature, current, gate resistor, gate voltage, load type (resistive or inductive), etc. Typically, the values provided by the manufacturer will not match exactly. If the test conditions are very similar, then the manufacturer’s datasheet may provide a reasonable estimate. The manufacturer does provide a plot of switching energy vs. load current based on inductive switching.

Fig. 3.29 shows MOSFET typical characteristic of gate-source voltage \( V_{GS} \), drain-source voltage \( V_{DS} \) and drain-source current \( I_{DS} \), and its definition of switching times and switching energies.

Fig. 3.29 Definitions of MOSFET switching times and energies

\( E_{on} \) is turn-on switching energy with diode, which is the integral of the product of drain current and drain-source voltage over the interval \( (t_{l_{on}}) \) from when the drain current starts to rise to when the voltage falls to zero in order to exclude any losses. \( E_{off} \) is Turn-off Switching Energy, which is the integral of the product of drain current and drain-
source voltage over the interval \( t_{i\text{,off}} \) starting from when the gate-source voltage drops below 90\% to when the drain current reaches zero.

In our circuit, MOSFETs operate at ZVS conditions, so there is no turn-on loss, which means \( E_{on} = 0 \).

Switching energy can be scaled directly for variation between application voltage and the datasheet switching energy test voltage. So if the datasheet tests were done at 330 Volts for example, and the application is at 400 Volts, simply multiply the datasheet switching energy values by the ratio 400/330 to scale.

MOSFET switching loss may be estimated by calculating the area underneath the \( V_{DS} \) and \( I_D \) waveforms and multiplying by the switching frequency and switching times.

The equations [67] below can be used as crude estimates of the area underneath the \( V_{DS} \) and \( I_D \) waveforms or the switching energy.

\[
E_{on} = \frac{1}{2} V_{DS} I_{DS} t_{i\text{,on}} \\
E_{off} = \frac{1}{2} V_{DS} I_{DS} t_{i\text{,off}} \\
\]

\[
P_{loss\_sw\_MOSFET} = \left( E_{on} + E_{off} \right) f_s
\]

Fig.3.30 shows IGBT typical characteristic of gate-emitter voltage \( V_{GE} \), collector-emitter voltage \( V_{CE} \) and collector current \( I_c \), and its definition of switching times and switching energies.

\[
E_{on} \text{ is Turn-On Switching Loss, which is the amount of total energy loss, including the loss from the diode reverse recovery, measured from the point where the collector current begins to flow to the point where the collector-emitter voltage completely falls to zero in }
\]

![Fig. 3.30 Definitions of IGBT switching times and energies](image)
order to exclude any conduction loss. $E_{\text{off}}$ is turn-off Switching Loss, which is the amount of total energy measured from the point where the collector-emitter voltage begins to rise from zero to the point where the collector current falls completely to zero.

In our circuit, IGBTs operate at ZCS conditions, so there is no turn-off loss, which means $E_{\text{off}} = 0$.

Similarly, IGBT switching loss may be estimated by calculating the area underneath the $V_{\text{CE}}$ and $I_C$ waveforms and multiplying by the switching frequency and switching times.

The equations [67] below can be used as crude estimates of the area underneath the $V_{\text{CE}}$ and $I_C$ waveforms or the switching energy.

$$E_{\text{on}} = \frac{1}{2} V_{\text{CE}} I_C t_{\text{on}}$$  (3.44)

$$E_{\text{off}} = \frac{1}{2} V_{\text{CE}} I_C t_{\text{off}}$$  (3.45)

$$P_{\text{loss \_sw \_IGBT}} = \left( E_{\text{on}} + E_{\text{off}} \right) f_s$$  (3.46)

Time and loss components which cannot be unambiguously described by the switching time definitions can be taken in consideration practically (e.g. the tail current characteristic for the IGBT).

### 3.6.5 Transformer Core Loss Analysis

Magnetic components such as inductors and transformers typically have core loss associated with them. The first step is to find the applied voltage-seconds. The voltage seconds is dependent on the duty cycle.

![Fig.3.31 An arbitrary voltage waveforms](image)

$$v(t)$$

area $\lambda$

$t_1$ $t_2$ $t$
An arbitrary periodic transformer primary voltage waveform $v(t)$ is illustrated in Fig.3.31. The volt-seconds applied during the positive portion of the waveform is denoted $\lambda$:

$$\lambda = \int_{t_1}^{t_2} v(t) \, dt$$

(3.47)

These volt-seconds, or flux-linkages, cause the flux density to change from its negative peak to its positive peak value. Hence, from Faraday’s law, the peak value ($\Delta B$) of the ac component of the flux density is

$$\Delta B = \frac{\lambda}{2 n_1 A_e}$$

(3.48)

$n_1 =$ Number of Primary Transformer Turns

$A_e =$ Effective Core Area of Transformer

Some key trends may be noticed from equations (3.46), (3.47):

- Increases in input voltage increases peak flux density.
- Increases in switching frequency decreases peak flux density.
- Increasing the number of primary turns decreases peak flux density

The peak flux density is dependent on applied voltage-seconds, primary transformer turns ratio, and effective core area. Since peak flux density is directly related to core loss, one can easily see how to modify the transformer design to reduce core loss. Typically, the input voltage cannot be changed but switching frequency can be increased to reduce applied voltage-seconds. Unfortunately, increases in switching frequency may lead to increased switching loss. Primary turns ratio can easily be increased as long as there is sufficient space, but resistance and losses will increase due to increased winding lengths. Larger cores may be used to increase effective core area but size and cost of the transformer will increase.

Once the ac peak flux density is known, the core loss can be estimated. The following equation for core loss calculation offers a close approximation.

$$P_L = af^c B^d$$

(3.49)
where $P_L$ is Power loss in $mW/cm^3$; $B$ is Peak flux density in kG; $f$ is frequency in kHz. In our circuit, a ferrite EE80 core is used and the loss parameters can be looked up in the table as follows provided by Magnetics Inc.

Table 3.3: factors applied to the above formula (3.49)

<table>
<thead>
<tr>
<th>Material type</th>
<th>Frequency range</th>
<th>$a$</th>
<th>$c$</th>
<th>$d$</th>
</tr>
</thead>
<tbody>
<tr>
<td>R Material</td>
<td>$f &lt; 100kHz$</td>
<td>0.074</td>
<td>1.43</td>
<td>2.85</td>
</tr>
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<td></td>
<td>$100kHz \leq f &lt; 500kHz$</td>
<td>0.036</td>
<td>1.64</td>
<td>2.68</td>
</tr>
<tr>
<td></td>
<td>$f \geq 500kHz$</td>
<td>0.014</td>
<td>1.84</td>
<td>2.28</td>
</tr>
<tr>
<td>P Material</td>
<td>$f &lt; 100kHz$</td>
<td>0.158</td>
<td>1.36</td>
<td>2.86</td>
</tr>
<tr>
<td></td>
<td>$100kHz \leq f &lt; 500kHz$</td>
<td>0.0434</td>
<td>1.63</td>
<td>2.62</td>
</tr>
<tr>
<td></td>
<td>$f \geq 500kHz$</td>
<td>7.36×10^{-7}</td>
<td>3.47</td>
<td>2.54</td>
</tr>
<tr>
<td>F Material</td>
<td>$f &lt; 10kHz$</td>
<td>0.790</td>
<td>1.06</td>
<td>2.85</td>
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<tr>
<td></td>
<td>$10kHz \leq f &lt; 10kHz$</td>
<td>0.0717</td>
<td>1.72</td>
<td>2.66</td>
</tr>
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<td>$10kHz \leq f &lt; 500kHz$</td>
<td>0.0573</td>
<td>1.66</td>
<td>2.68</td>
</tr>
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<td></td>
<td>$f \geq 500kHz$</td>
<td>0.0126</td>
<td>1.88</td>
<td>2.29</td>
</tr>
<tr>
<td>J Material</td>
<td>$f \leq 20kHz$</td>
<td>0.245</td>
<td>1.39</td>
<td>2.50</td>
</tr>
<tr>
<td></td>
<td>$f &gt; 20kHz$</td>
<td>0.00458</td>
<td>2.42</td>
<td>2.50</td>
</tr>
<tr>
<td>W Material</td>
<td>$f \leq 20kHz$</td>
<td>0.300</td>
<td>1.26</td>
<td>2.60</td>
</tr>
<tr>
<td></td>
<td>$f &gt; 20kHz$</td>
<td>0.00382</td>
<td>2.32</td>
<td>2.62</td>
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<td>H Material</td>
<td>$f \leq 20kHz$</td>
<td>0.148</td>
<td>1.50</td>
<td>2.25</td>
</tr>
<tr>
<td></td>
<td>$f &gt; 20kHz$</td>
<td>0.135</td>
<td>1.62</td>
<td>2.15</td>
</tr>
</tbody>
</table>

Then we can estimate approximately the total core loss as follows.

$$P_{fe} = P_L V_c = a f^c B^d A_e l_m$$

(3.50)

$A_e =$ Effective Core Area of Transformer (cm$^2$)

$l_m =$Magnetic path length (cm)

Like many other devices components, core loss is heavily dependent on temperature. The transformer core temperature coefficient varies and may be negative or positive over different temperature ranges. At low temperatures, the core loss is typically high. The core
loss decreases as temperature increases. At a certain point, there is an inflection point and the core loss increases again as temperature increases. The temperature range that minimizes the core loss is dependent on the material of the core. The core loss variation due to temperature is also dependent on frequency and peak flux density which core loss estimations even further.

3.6.6 Transformer Copper Loss Analysis

Transformers also have copper loses in addition to core losses. The copper losses are increased further due to skin and proximity effects if the transformer is not properly designed. Copper loss simply due to current is easy to estimate, but the loss estimation becomes substantially more difficult when other factors such as skin effect and proximity effects are considered. Ignoring the copper losses due to skin and proximity effects, the total copper loss can be expressed in the form

$$P_{cu} = \frac{\rho (MLT) n_t^2 I_{tot}^2}{W_A K_u}$$

(3.51)

Combining equations (47) and (49), it yields

$$P_{cu} = \left( \frac{\rho A^2 I_{tot}^2}{4 K_u} \right) \left( \frac{MLT}{W_A A_c^2} \right) \left( \frac{1}{\Delta B} \right)^2$$

(3.52)

$I_{tot} = \sum_{j=1}^{k} \frac{n_j}{n_1} I_j$, is the sum of the rms winding currents, referred to the primary winding.

$$\rho = \text{Resistivity of copper} = 1.724 \times 10^{-6} \, \Omega \cdot cm @ 25^\circ C \text{ and } 2.3 \times 10^{-6} \, \Omega \cdot cm @ 100^\circ C.$$  

$MLT = \text{Mean length per turn}.$

$n_1 = \text{Number of primary winding turns}.$

$W_A = \text{Bobbin winding area}.$

$K_u = \text{Winding fill factor, is the fraction of the core window area that is filled with copper}.$

The dc resistance of a transformer winding can be calculated with the following equation.

$$R = \rho \frac{l}{A_c}$$

(3.53)

$l = \text{Length of winding}$

$A_c = \text{Cross-sectional area of copper}$
Under given core type and size, winding turns and the wire that is used, we can look up the data we need from the core data and wire gauge data provided by the manufacturer. The DC resistance of primary and secondary windings can also be obtained as follows.

The DC winding resistance for the primary side is:

\[
R_{pri} = n_1 (MLT) \left( R_{pri\_AWG\#} \right)
\]  

(3.54)

The DC winding resistance for the secondary side is

\[
R_{sec} = n_2 (MLT) \left( R_{sec\_AWG\#} \right)
\]  

(3.55)

If the primary and secondary currents are known, then the total copper loss is given

\[
P_{cu} = I_{pri}^2 R_{pri} + I_{sec}^2 R_{sec}
\]  

(3.56)

\(_n_1 = \text{Number of primary winding turns.} \\
_n_2 = \text{Number of secondary winding turns.} \\
R_{pri\_AWG\#} = \text{the primary wire resistance in } 10^{-6} \Omega/cm. \\
R_{sec\_AWG\#} = \text{the secondary wire resistance in } 10^{-6} \Omega/cm.

Losses such as core loss, contact loss, and copper loss, create heat and raise the temperature of the transformer windings. This in turn causes copper losses to increase. The increase in temperature also makes copper more susceptible to skin effect. Skin effect can greatly increase the effective resistance of a high frequency transformer winding and, therefore, creating additional losses. Even if wire is selected such that skin depth matches the copper thickness, the current density varies throughout the depth. Therefore, greater amounts of current will flow at the surface and less current at the center of the conductor. The conductor is still not fully utilized and therefore, the effective resistance will increase.

3.6.7 Inductor Loss

Inductors dissipate power in the core and in the windings. Though determining these losses with precision can require complex measurements, an easier alternative exists. Inductor losses may be estimated using readily available data from core and inductor suppliers along with the relevant power supply application parameters.

The power loss of an inductor is defined by the basic formula:

\[
P_{loss\_inductor} = P_{core} + P_{dcr} + P_{acr}
\]  

(3.57)
The calculated and/or measured core loss, $P_{core}$, is often directly provided by the inductor supplier. If not, a formula can be used to calculate the core loss. First of all, the ac peak flux density (B in Tesla) needs to be obtained and it is given as follows.

$$B = \frac{N \Delta I}{\mu l_e}$$  \hspace{1cm} (3.58)

where

$N$ = number of turns

$l_e$ = effective magnetic length

Measuring core loss and getting repeatable results can be a tedious task depending on the test frequency. A general form of the core loss formula for ferrite cores is:

$$P_{core} (mW) = a f^x B^y V_e$$  \hspace{1cm} (3.59)

where:

$a$ = Constant for core material

$f$ = Frequency in kHz

$B$ = Peak Flux Density in kGauss

$x$ = Frequency exponent

$y$ = Flux Density exponent

$V_e$ = Effective core volume (cm$^3$)

The core loss can be calculated by entering the ‘$a$’ coefficient and the frequency and flux density exponents, which are unique to each core material. For example, in this circuit, high flux core is used and B in the formula is in Tesla and the core loss density curves can be obtained from the supplier (Magnetics) as shown in Fig.3.32.

![Core Loss Density Curves](image)

**Fig. 3.32 Core loss density curves of the output inductor**
The wire loss \( P_{dcr} \) caused by dc resistance is easy to calculate. It is defined by this basic formula:

\[
P_{dcr} = I_{rms}^2 R_{dc}
\]  

(3.60)

where:

- \( I_{rms} \) = Therms value of the peak current applied to the inductor
- \( R_{dc} \) = The dc resistance of the inductor

The wire loss \( P_{acr} \) caused by ac resistance is more difficult to calculate since ac winding resistance values are not always readily available from magnetics vendors. \( P_{acr} \) is defined by the following formula:

\[
P_{acr} = I_{rms}^2 R_{ac}
\]  

(3.61)

where:

- \( I_{rms} \) = Therms value of the peak-peak ripple current applied to the inductor
- \( R_{ac} \) = The ac resistance of the inductor

In many cases \( P_{acr} \) is a small percentage of the overall inductor power loss, thus, the power loss of an inductor is defined by the simple formula

\[
P_{loss\_inductor} = P_{core} + P_{dcr}
\]  

(3.62)

3.6.8 Other Losses

Calculating power loss for the snubber is rather difficult since it can be dependent on switching characteristics. When full ZVS condition is obtained, the snubber loss decreases due to less severe perturbations. Hard switching conditions create heavy voltage spikes and ripples, which must be damped by the snubber.

Many other parasitic losses exist within the system. For example, capacitor ESR is a concern, particularly for high current systems. Capacitors are important for maintaining waveform quality and reducing voltage spikes and ripples. These capacitors may have to supply and draw large amounts of current. The capacitor ESR losses can become significant when the current is large. Parallelizing additional capacitors can help reduce losses due to capacitor ESR since RMS current through individual capacitors is reduced.

Another source of loss, which is difficult to be estimated is parasitic inductance. Parasitic inductance can cause excessive voltage spikes during switching. Switching waveforms affected will see larger losses in addition to higher voltage stress. Higher
voltage stress may lead to device failure. If higher voltage rating devices are used, typically conduction loss of the device increases since the voltage rating has increased.

Termination is another major parasitic loss, especially for high current situation. Each mechanical connection made introduces termination losses. Mechanical connections do not have perfect contact and a small resistance exists between the two contacts. Ideally, mechanical contacts should be eliminated where possible and one piece of copper should be used for connection. The mechanical contacts may have a small resistance but the loss can become very high due to the large currents of high current systems. The loss would be simple to calculate with the conduction loss equation, but the resistance is difficult to predict since the resistance is due to the physical construction. Under high current conditions, the terminals can get hot due to the power loss. The higher temperature increases the resistance of copper, further increasing parasitic losses. In addition to mechanical contact resistance, the resistance increases further if two different materials are used for contacts.

Skin effect and proximity effect can also create significant amounts of loss. Skin effect raises the effective resistance of the transformer winding. Since large currents are flowing through the transformer, an increase in resistance can create large amounts of loss.

### 3.6.9 Efficiency Estimation

Based on the loss estimations above, the efficiency can be estimated. Once again, the temperature and other factors have a significant effect on system efficiency. For this estimation, the following conditions will be assumed.

<table>
<thead>
<tr>
<th>Table 3.4: Efficiency estimation conditions</th>
</tr>
</thead>
<tbody>
<tr>
<td><strong>Input Voltage</strong></td>
</tr>
<tr>
<td><strong>Output Voltage</strong></td>
</tr>
<tr>
<td><strong>Maximum Output Power</strong></td>
</tr>
<tr>
<td><strong>Switching frequency</strong></td>
</tr>
</tbody>
</table>

The total power loss can be calculated shown in Fig.3.33 (a) and the efficiency of the system can be estimated shown in Fig.3.33 (b).
As an example, specifically the estimated power losses at 3.4-kW rated output power with two different output voltage levels are listed in the Fig. 3.34. It indicates that the output diodes and IGBTs are the dominant sources of the power losses under full-load condition.

3.7 Topology Variations

Fig.3.35 demonstrates several ZVZCS full-bridge combining resonant half-bridge converters with different rectifier configurations, which share the common feature that the full-bridge converter changes to half-bridge converter and keeps transferring energy from the input to the output during the freewheeling interval of the output inductor. It is worth to
note that the resonant converter can be half-bridge or full-bridge or other high efficiency parallel or series or multi-element resonant converters, and that the switches leg configuration can be two-level or three-level with IGBT or MOSFET or hybrid devices.

Fig. 3.35 Several variations hybrid resonant and PWM converters
3.8 Implemented Hardware

3.8.1 Complete Circuit Structure

Fig. 3.36 shows the complete circuit structure of the implemented hardware, including PFC circuit, control circuit, hybrid resonant and PWM converter, and output.

![Fig.3.36 Complete structure of the implemented hardware](image)

3.8.2 Implemented Hardware Prototype

The following in Fig. 3.37 is the implemented hardware prototype.

![Fig.3.37 Prototype of the implemented hardware](image)

3.8.3 Experimental Verification

A 3.4 kW hardware prototype for battery charger has been designed, fabricated and tested to verify the circuit validity and the improved performance of the proposed converter. The prototype converter has the following specifications: Input voltage $V_{in}=380\text{V} - 400\text{V}$;
Output voltage $V_o = 250V - 450V$; Maximum output current $I_{o,\text{max}} = 15A$; Switching frequency $f_s = 46.7kHz$.

Fig. 3.38 Power circuit and the parameters of the prototype

Fig. 3.38 shows the power circuit and the parameters of the prototype with the part numbers of the components used. All power semiconductor devices including MOSFETs (S1 and S2), IGBTs (S3 and S4) and diodes (D1~D7) are mounted on the heat-sink with the same TO247 package. The transformer TR1 is designed with tightly coupling and without airgap in the Ferrite EE80 core (magnetizing inductance $L_{m1} = 7.1mH$, leakage inductance $L_{li1} = 3.9\mu H$), and the transformer TR2 with loosely coupling and airgap in the core (magnetizing inductance $L_{m2} = 566\mu H$, leakage inductance $L_{li2} = 35\mu H$).

ZCS operation of the main device IGBT is verified by the experimental waveforms of the IGBT (S4) voltage $V_{ce4}$, device current $i_{ce4}$, and gate voltage $G_4$, shown in Fig. 3.39. Before the gate is turned off, the device current $i_{ce4}$ is nearly zero, so the IGBT operates at zero-current switching condition in the worst case of the maximum output power.

![Experimental waveforms of IGBT ZCS](image)

Fig. 3.39 IGBT ZCS experiment waveforms of device voltage, current, and its gate.
Fig. 3.40 shows the experimental verification of the MOSFETs main switches ZVS operation with load current adaptability. Fig. 3.40 (a) shows the device MOSFET, S2, drain-to-source voltage $v_{ds2}$ and its gating signal $G_2$ at no load condition, and Fig. 3.40 (b) shows $v_{ds2}$ and $G_2$ at the full load current condition (8.8A). The gate voltage is 15V for turn on and -5V for turn off. By observing that $v_{ds2}$ drops to zero before $G_2$ turns ON at different output current levels, both figures clearly indicate that ZVS is achieved from zero to full load.

The fast reset of the circulating current of the transformer TR1 during the output inductor freewheeling interval is illustrated in Fig. 3.41. The secondary side current $i_{sec1}$ of transformer TR1 drops to zero in 0.7µs with the low leakage inductance because that ZVS of MOSFET can be achieved in the proposed converter even while the leakage inductance is zero. It also can be seen that full-bridge diode D1 is turned off under relatively low voltage without severe reverse current.

(a) zero load (b) full load $I_o=8.8$A

Fig. 3.40 MOSFET ZVS load adaptability experiments with different load conditions

Fig. 3.41 Full-bridge diode D1 waveforms of voltage, current and its associated transformer secondary current.

Fig. 3.42 shows tested waveforms of the half-bridge diode ZCS turn-on and turn-off in the worst case of the maximum output current. The well-clamped voltage stress and ZCS
operation of the half-bridge diode imply that the diode voltage stress is low and the low-voltage drop diode can be utilized to further improve the efficiency.

![Half-bridge diode experimental waveforms](image)

Fig. 3.42 Half-bridge diode D5 experimental waveforms of voltage and its associated transformer secondary current.

The measured efficiency at different loads under the condition of 46.7 kHz switching frequency, 390 V input, 385 V and 280 V output is given in Fig. 3.43. It can be seen that high efficiency over wide load current and output voltage range is achieved. The efficiency with load range from 20% to 100% maintains 96% or higher, and the maximum efficiency achieves 98% under the conditions of 385V output voltage and 3.4 kW output power. The efficiency is higher with a higher output voltage because that the conduction losses of the active switches and output diodes are reduced with the lower current stresses.

![Efficiency vs. Output Power](image)

Fig. 3.43 Experimental results of efficiency as a function of the output power.

### 3.9 Summary

A novel hybrid resonant and PWM converter combining resonant half-bridge and phase shifted full-bridge topology has been proposed to achieve high efficiency and true full soft-
switching range, which is also verified by a 3.4 kW hardware prototype. Table 3.2 summarizes the factors that determine the performances of the three converters.

Table 3.5: phase-shifted full bridge, LLC and Proposed Converters

<table>
<thead>
<tr>
<th></th>
<th>Control method</th>
<th>ZVS range</th>
<th>Circulating current</th>
<th>Constant Current and Voltage</th>
<th>Output diode voltage stress</th>
</tr>
</thead>
<tbody>
<tr>
<td>PS FB</td>
<td>Fixed frequency</td>
<td>Limited range</td>
<td>High</td>
<td>Yes</td>
<td>High</td>
</tr>
<tr>
<td>LLC</td>
<td>Variable frequency</td>
<td>Full range</td>
<td>Low</td>
<td>No</td>
<td>Low</td>
</tr>
<tr>
<td>Proposed converter</td>
<td>Fixed frequency</td>
<td>Full range</td>
<td>Low</td>
<td>Yes</td>
<td>Low</td>
</tr>
</tbody>
</table>

NOTE: PS HB represents phase-shifted full bridge converter; LLC represents LLC converter; $L_{lk1}$ is Leakage inductance of the transformer in PS FB; $L_{m2}$ is Magnetizing inductance the transformer in LLC; $L_{f}$ is Output inductor; $R_o$ is output load.

From Table 3.5 and Fig.3.44, it can be seen that the proposed hybrid converter can realize the full range ZVS by designing suitable magnetizing inductance $L_{m2}$ used in LLC and the leakage inductance $L_{lk1}$ of the transformer used in phase-shifted full bridge called main transformer TR1 is independent of the ZVS. Since $L_{lk1}$ is no longer related to the ZVS, it can be minimized to reduce the duty cycle loss and circulating current.

\[
slope = \frac{(n_1 - n_2)V_{in}}{L_{lk1}}
\]

\[
slope = \frac{(n_1V_{in} - V_o)}{(L_o / n_1)}
\]

\[
slope = \frac{-n_2V_{in}}{L_{lk1}}
\]

Fig.3.44 Key waveforms and formula of the proposed hybrid converter

The distinctive features of the proposed circuit are summarized as follows:
1) With the parallel LLC resonant half-bridge configuration, zero-voltage switching of MOSFETs in the leading-leg can be ensured from true zero to full load, and thus, the super-junction MOSFET with slow reverse recovery body diode can be reliably used.

2) IGBTs in the lagging-leg work at zero-current switching with minimum circulating conduction loss because the parallel secondary-side DC voltage source effectively reset the circulating current, therefore, the turn-off loss and the conduction loss of the IGBTs are significantly reduced.

3) Duty cycle loss is negligible since the leakage inductance of the main transformer can be minimized without losing ZVS operation, thus, the current stresses through the primary-side semiconductors are minimized by the optimized turns ratio of the main transformer.

4) The topology is suitable for wide-range output voltage or current source applications because of the buck-type configuration with the simple phase-shift pulse width modulation, and thus, it is a good candidate for the electrical vehicle battery charger.
CH4: Improved Hybrid Resonant and PWM Converter

4.1 Issues in Previous Hybrid Resonant and PWM Converter

The hybrid LLC resonant and phase-shifted full bridge PWM converter described in CH3 is repeated here as shown in Fig.4.1 (a) and the key operation waveforms is shown in Fig. 4.1(b).

From Fig.4.2, it can be concluded that if the effective duty cycle is large for the main transformer, the energy stored in capacitor C1 or C2 charged by LLC converter has no chance to be transferred to the output, which means the utilization efficiency of the auxiliary
transformer is very low in this case. When it is high power application, it requires the duty cycle large, then the auxiliary transformer TR₂ charges the capacitor C₂ or C₁ while the main transformer TR₁ is transferring the energy to the output load. So the issue is how to get the auxiliary transformer TR₂ utilized more efficiently?

4.2 The Improved Hybrid Resonant and PWM Converter

Fig.4.3 is a solution for the previous issues, in which the output of the LLC resonant converter is in series with the output load, theoretically transferring energy to the output all the time.

4.2.1 Operational Principles

Fig.4.4 (a) show the circuit diagram of the improved Hybrid Resonant and PWM Converter which composed of two parts similar to the previous hybrid resonant and PWM converter: 1) the resonant half-bridge circuit including two MOSFETs S₁ and S₂, loosely coupled transformer TR₂, resonant capacitor C₃, and the secondary rectifier D₅, D₆, and C₁, C₂; 2) the phase shifted full-bridge circuit including two MOSFETs S₁ and S₂ as leading-lag, two IGBTs as lagging-leg, tightly coupled transformer TR₁, the secondary rectifier D₁~4, and the LC output filter. The topology operating principle can be explained by the gating sequence and associated key voltage and current waveforms shown in Fig.4.4 (b).

Where $C_{S1}$, $C_{S2}$ are the equivalent capacitance of the MOSFETs S₁, S₂, respectively; $v_{rect}$ is voltage of the output inductor left-side point referred to the output ground; $V_o$ is the output voltage; $i_{pri1}$ and $i_{pri2}$ are the primary current of the transformer TR₁ and TR₂ respectively; $i_{Lm2}$ is the magnetizing current of the transformer TR₂; and the $v_{ds1}$ is the device S₁ drain-to-source voltage.
This improved Hybrid Resonant and PWM Converter combines the behavior of two different converter topologies: LLC half-bridge converter operating at the load-independent resonant frequency which makes the circuit operate at optimal condition to achieve maximum efficiency and the constant frequency phase shifted full-bridge converter which is used to regulate the output by means of the phase shift. The most important is that the
output of the LLC half bridge is in series with the output of the converter, thus the auxiliary transformer TR2 can get improved greatly. Whatever the duty cycle is, the energy stored in the capacitor C2 or C1 through the auxiliary transformer TR2 can be transferred to the output load. There are six distinct operation modes for this topology in the PWM half cycle, as shown as Fig.4.5.

Mode \([t_0, t_1]\): At \(t_0\), the secondary current of transformer TR1 reaches at the reflected output inductor current. Switches S3 and S2 remain on. Suppose the leakage inductance of the main transformer is zero, that is \(L_{ik1} = 0\). Thus, the equivalent circuit at this interval is shown in Fig.4.6, as well as the key waveforms.

\[
v_{sec2} = n_2 \cdot \left( \frac{1}{2} V_{in} \right) = V_{c1} = V_{c2}
\]

where \(n_2\) is the secondary-to-primary turns ratio of TR2.

Clearly from Fig.4.6 (a), the reflected input voltage applies to the left-side of the output inductor called the rectified voltage, \(v_{rect}\), which can be expressed as

\[
v_{rect} = n_1 \cdot V_{in} + \frac{1}{2} n_2 V_{in}
\]

where \(n_1\) is the secondary-to-primary turns ratio of TR1. \(v_{rect}\) is the rectified voltage and \(V_{in}\) is input voltage shown in Fig.4.4. The primary current of the main transformer reaches the reflected current of the output inductor, \(L_{o}\), and increases with the slope as
\[ \frac{di_{\text{pri}}}{dt} = \left( n_1 V_{\text{in}} + \frac{1}{2} n_2 V_{\text{in}} - V_o \right) / \left( L_o / n_1 \right) \] (4.3)

Suppose output capacitors, \( C_1 \) and \( C_2 \), are large enough. Thus, the primary side of Fig.4.6 (b) can be simplified as Fig.4.7 as follows.

\[ \frac{di_{Lm2}}{dt} = \frac{V_{\text{in}}}{2 L_m} \] (4.4)

where \( n_2 \) are the secondary-to-primary turns ratio \( T_{R2} \). Thus,

\[ i_{Lm2}(t) = i_{Lm2}(t_0) + \frac{V_{\text{in}}}{2 L_m}(t-t_0) \] (4.5)

\( i_{Lm2}(t_0) \) is the current flowing the resonant capacitor \( L_{m2} \) at \( t_0 \).

Since the circuit operates at resonant frequency, where the voltage gain is constant, a little bit higher than unity, which is independent of load and ratio of \( m = L_m / L_{kL} \), \( L_m \) is the transformer magnetizing inductance and \( L_{kL} \) is the transformer leakage inductance, \( L_{m2} \) can be relatively large as needed. Suppose output capacitors, \( C_1 \) and \( C_2 \), are large enough. Then the secondary side of Fig.4.6 (b) can be simplified as Fig.4.8 as follows.

\[ \frac{i_s}{n_2} \]
\[ i_x = \left[ \frac{V_{in}}{2} - V_{c3}(t_0) \right] \sin \left[ \omega_r \left( t - t_1 \right) \right] \]  (4.6)

Thus, the auxiliary transformer primary current, \( i_{pri2} \), which increases with resonance between the leakage inductor, \( L_{lk2} \), and the resonant capacitor, \( C_3 \), is given by

\[ i_{pri2} = \left[ \frac{V_{in}}{2} - V_{c3}(t_0) \right] \sin \left[ \omega_r \left( t - t_1 \right) \right] + i_{Lm2}(t) \]  (4.7)

where \( Z_o = \sqrt{L_{lk2} / C_3} \) and \( \omega_r = \frac{1}{\sqrt{L_{lk2} C_3}} \), \( V_{c3}(t_0) \) is the voltage across the resonant capacitor \( C_3 \) at \( t_0 \).

Mode \([t_1, t_3]\): At \( t_1 \), \( S_2 \) is turned off by the PWM command, and the sum of two transformers primary current will charge and discharge the MOSFET capacitors \( C_{s2} \) and \( C_{s1} \), respectively. At \( t_2 \), \( C_{s1} \) and \( C_{s2} \) can be fully discharged and charged under any output current condition due to load-independent magnetizing current \( i_{Lm2} \), then the body diode of switch \( S_1 \) is on, thus \( S_1 \) can be turned on at zero-voltage condition at interval \([t_2, t_3]\). With \( C_{s1} \) being discharged, switch voltage \( v_{ds1} \) starts falling. The energy stored in \( C_1, C_2 \) is transferred to the output load.

At interval \([t_1, t_2]\), the MOSFET capacitors \( C_{s2} \) and \( C_{s1} \) get charged and discharged, respectively. Under zero-load condition which is the worst case for this circuit, the main transformer (TR1) primary current is zero, \( i_{pri1} = 0 \) and the auxiliary transformer (TR2) primary current, \( i_{pri2} \), is designed to have the ability to fully charge and discharge the output capacitors of the switches to guarantee the devices under ZVS condition.

Fig.4.9 The equivalent circuit under zero load condition (worst case)

Fig.4.9 shows how the circuit guarantees the devices under ZVS condition only if the \( L_m \) is designed well to guarantee the current, \( i_{Lm2} \), is big enough to fully charge and
discharge the output capacitors of the switches.

In this case, \( L_{m2} \) is resonant with \( C_{s1}/C_{s2} \) and the maximum resonant time is a quarter of the switching period.

\[
v_{ds1} = V_{in} \cos \left[ \frac{\omega_{m2} (t - t_1)}{4} \right]
\]  

(4.8)

where \( \omega_{m2} = \frac{1}{\sqrt{L_{m2} (C_{s1} + C_{s2})}} \)

The rectified voltage, \( v_{\text{rect}} \), starts falling to the valley as

\[
v_{\text{rect}} = n_2 \cdot V_{in}
\]

(4.9)

At interval \([t_2, t_3]\): The body diode of \( S_1 \) is on and switch \( S_1 \) voltage \( v_{ds1} \) is zero. The TR\(_1\) primary current starts to be resetting effectively by the parallel secondary-side DC voltage source produced by LLC half-bridge converter. The equivalent circuit at this interval is shown in Fig.4.10, as well as the key zoomed waveforms.

![Equivalent Circuit and Waveforms](image)

Fig.4.10 (a), (b) the equivalent circuit for Mode \([t_2, t_3]\); (c) the key zoomed waveforms

From Fig.4.10, it can be seen that the primary current of the main transformer decreases with the slope as follows.

\[
-\frac{di_{\text{pri1}}}{dt} = \frac{n_2}{2n_1} V_{in} \left/ \frac{L_{lk1}}{L_{lk1}} \right.
\]

(4.10)

Since \( L_{lk1} \) can be designed very small because there is no need to consider the tradeoff resulting from \( L_{lk1} \) in this proposed circuit, the resetting time can be very short.

And the magnetizing current \( i_{Lm2} \) starts to decrease with a constant slope as
\[
\begin{align*}
\frac{di_{Lm2}}{dt} &= \frac{V_{in}}{2} \frac{1}{L_m} \\
&= (4.11)
\end{align*}
\]

Mode \([t_3, t_5]\): At \(t_3\), \(S_1\) can be turned on under zero-voltage condition by PWM command. The gate of \(S_3\) remains on but no current flowing through \(S_3\). At \(t_4\), the switch \(S_3\) turns off by PWM command under zero current condition since the transformer \(TR_1\) current keeps zero. The energy stored in \(C_1, C_2\) is transferred to the output load.

Mode \([t_5, t_6]\): At \(t_5\), IGBT \(S_4\) is turned on. The \(TR_1\) secondary current value starts increasing until it arrives at current level of the output inductor. The equivalent circuit at this interval is shown in Fig.4.11, as well as the key zoomed waveforms.

From Fig.4.11, it can be seen that the slope of the \(TR_1\) primary current can be simply expressed as
\[
\begin{align*}
\frac{-di_{pri1}}{dt} &= \frac{n_1 - 0.5n_2}{n_1} \frac{V_{in}}{L_{lk1}} \\
&= (4.12)
\end{align*}
\]

where \(n_1\) and \(n_2\) are the secondary-to-primary turns ratio of \(TR_1\) and \(TR_2\) respectively; \(L_{lk1}\) is the primary leakage inductance of \(TR_1\) and \(i_{pri1}\) is the primary current of the main transformer \(TR_1\). Duty cycle loss occurs during this interval. This proposed circuit can have the potential to get very small duty cycle loss because the leakage inductance of the main transformer is independent of the zero-voltage-switching and can be minimized.

4.2.2 Design Considerations

The design considerations and steps are the same as the one proposed in chapter 3, but some of results are different and better as follows.
All the other circuit parameter designs are referred to chapter 3.

a) Transformers Turns Ratio

According to the voltage-second balance across the output inductor and the secondary rectifier voltage waveform shown in Fig. 4.12, we can obtain

\[
(n_1V_{in} + 0.5n_2V_{in} - V_o)D_{eff} = (V_o - n_2V_{in}) (1 - D_{eff})
\]  

where \(D_{eff}\) is the effective duty cycle.

\[
\text{Fig.4.12 The secondary rectifier voltage waveform}
\]

Then, the steady state voltage gain in continuous conduction mode can be described as

\[
\frac{V_o}{V_{in}} = D_{eff} \left( n_1 - 0.5n_2 \right) + n_2
\]

where \(n_2 < n_1\). This equation shows that the voltage gain varies between \(n_2\) (when \(D=1\)) and \(n_1\) (when \(D=0\)) as illustrated in Fig.4.13.

\[
\text{Fig.4.13 Voltage gain vs. effective duty cycle}
\]

Therefore, the secondary-to-primary turns ratio \(n_1\) of TR1 and \(n_2\) of TR2 should be chosen as

\[
n_1 = V_{o,\text{max}} / V_{in,\text{min}} - 0.5V_{o,\text{min}} / V_{in,\text{max}}
\]

\[
n_2 = V_{o,\text{min}} / V_{in,\text{max}}
\]

b) Duty Cycle Loss

From Fig.4.14 and the topology mode \([t_5, t_6]\) shown in Fig.4.5, the duty cycle loss seen by the output inductor can be derived as

\[
\Delta D_{loss} = \frac{2n_1^2L_{lk1} \cdot I_o \cdot f_s}{(n_1 - 0.5n_2) \cdot V_{in}}
\]  

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where $I_o$ is the output current. It is clear from the equation (17) that if $L_{lk1}$ is close to zero, the duty cycle loss is close to zero. Here, $L_{lk1}$ can be designed very small because the zero-voltage-switching range is independent of the value of $L_{lk1}$ in this circuit.

![Diagram of rectifier waveforms](image)

**Fig. 4.14** Waveforms of rectified voltage $v_{rect}$, main transformer TR1 primary voltage $v_{pri1}$ and main transformer TR1 primary current $i_{pri1}$

Suppose $n_1$ and $n_2$ are the secondary-to-primary turns ratio of TR1 and TR2 in the proposed one in chapter 3, respectively, and then the equation (4.17) becomes

$$\Delta D_{loss} = \frac{2(n_1 - 0.5n_2)^2 L_{lk1} \cdot I_o f_s}{(n_1 - n_2) \cdot V_{in}}$$  \hspace{1cm} (4.18)

**c) Output Inductance**

Fig.4.15 (a) is the rectified voltage waveform of the conventional full bridge converter. The peak-to-peak current ripple can obtained from chapter3, repeated here as follows.

$$\Delta i_{1pk-pk}(V_o) = \frac{T_s}{n_1 L_o} (n_1 - \frac{V_o}{V_{in}}) V_o$$  \hspace{1cm} (4.19)

Fig.4.15 (b) is the rectified voltage waveform of the proposed converter. The peak-to-peak current ripple can obtained from chapter3, repeated here as follows.

$$\Delta i_{2pk-pk}(V_o) = \frac{V_{in} T_s}{(n_1 - n_2) L_o} (n_1 - \frac{V_o}{V_{in}})(\frac{V_o}{V_{in}} - n_2)$$  \hspace{1cm} (4.20)

(a) Conventional FB converter; (b) the proposed converter; (c) the improved converter

**Fig. 4.15** Voltage waveforms of rectifier
Fig. 4.15 (c) is the rectified voltage waveform of the improved converter. The peak-to-peak current ripple can be expressed as

\[
\Delta i_{3, pk-pk} (V_o) = \frac{V_{in} T_s}{(n_1 - 0.5n_2)L_o} (n_1 + 0.5n_2 - \frac{V_o}{V_{in}}(\frac{V_o}{V_{in}} - n_2))
\]

(4.21)

By solving the equations (21) and (19), it yields

\[
\frac{\Delta i_{3, pk-pk, max}}{\Delta i_{1, pk-pk, max}} = 1 - \frac{n_2}{2n_1}
\]

(4.22)

Suppose \(n_1\) and \(n_2\) are the secondary-to-primary turns ratio of TR1 and TR2 in the proposed one in chapter 3, respectively, and then the equation (4.22) becomes

\[
\frac{\Delta i_{3, pk-pk, max}}{\Delta i_{1, pk-pk, max}} = 1 - \frac{n_2}{n_1 + (n_1 - n_2)}
\]

(4.23)

And the ratio of the proposed one in Chapter 3 to the conventional one is repeated as follows.

\[
\frac{\Delta i_{2, pk-pk, max}}{\Delta i_{1, pk-pk, max}} = 1 - \frac{n_2}{n_1}
\]

(4.24)

where \(n_2 < n_1\). And given \(n_2:n_1=4:9\), the relationship of the normalized output voltage and normalized output inductor peak-to-peak current is shown in Fig. 4.16.

Fig. 4.16 Normalized peak-to-peak output inductor current vs. normalized output voltage.

It can be seen from Fig.4.16 that the output inductor current ripple in the proposed converter can be reduced by \(n_2/n_1\) compared to the conventional full bridge, which means the inductance can be reduced by \(n_2/n_1\) compared to the conventional full bridge under the same current ripple condition, and the output inductor current ripple in the improved converter can be reduced by \(n_2/(2n_1-n_2)\) compared to the conventional full bridge, which
means the inductance can be reduced by \( n_2/(2n_1-n_2) \) compared to the conventional full bridge under the same current ripple condition. Since \( n_2<n_1 \), it can be seen that the improved converter has smallest current ripple.

### 4.3 Simulation Verification

Based on the previous analysis, the circuit is designed and the simulation circuit is shown in Fig.4.17. Correspondingly, the simulation results are given at full load (worst case for IGBTs ZCS condition) and no load (worst case for MOSFETs ZVS condition) shown in Figs.4.18~22.

![Fig.4.17 Power stage of the simulation circuit](image)

The specifications are given in table 4.1 as follows.

<table>
<thead>
<tr>
<th></th>
<th>Full load</th>
<th>No load</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>( worst case for IGBT ZCS )</td>
<td>( worst case for MOSFET ZVS )</td>
</tr>
<tr>
<td>Input Voltage</td>
<td>390V</td>
<td>390V</td>
</tr>
<tr>
<td>Output Voltage</td>
<td>385V</td>
<td>385V</td>
</tr>
<tr>
<td>Output Power</td>
<td>6.6kW</td>
<td>0W</td>
</tr>
<tr>
<td>Switching Frequency</td>
<td>46.7kHz</td>
<td>46.7kHz</td>
</tr>
</tbody>
</table>

From Fig.4.18, it can be seen that ZCS operation of the main device IGBTs is verified by the simulation waveforms of the IGBT \((S_4)\) voltage \(V_{ce4}\), device current \(i_{c4}\), and gate
voltage $G_4$. Before the gate is turned off, the device current $i_{c4}$ is zero, so the IGBT operates at zero-current switching condition in the worst case of the maximum output power.

Fig.4.18 IGBT waveforms of the voltage, current, and its gate at full load

It can be seen from Figs. 4.19, 4.20 that the main switches of MOSFETs demonstrate ZVS operation with load current adaptability. Fig.4.20 shows the device MOSFET, $S_2$, drain-to-source voltage $v_{ds2}$ and its gating signal $G_2$ at the full load condition and Fig.4.21 shows $v_{ds2}$ and $G_2$ at no load current condition. By observing that $v_{ds2}$ drops to zero before $G_2$ turns ON at different output current levels, both figures clearly indicate that ZVS is achieved from true zero to full load.

Fig.4.19 MOSFET waveforms of the voltage, current, gate and output current at full load
Fig. 4.20 MOSFET waveforms of the voltage, current, gate and output current at no load

The fast reset of the circulating current of the transformer TR1 during the output inductor freewheeling interval is illustrated in Fig. 4.21. The secondary side current $i_{sec1}$ of transformer TR1 drops to zero in 0.7µs with the low leakage inductance because that ZVS of MOSFET can be achieved in the converter even while the leakage inductance is zero. It also can be seen that full-bridge diode D1 is turned off under relatively low voltage without severe reverse current.

Fig. 4.21 Full-bridge diode D1 waveforms of voltage, current and its associated transformer secondary current at full load
Fig. 4.22 shows the waveforms of the half-bridge diode ZCS turn-on and turn-off in the worst case of full load condition. The well-clamped voltage stress and ZCS operation of the half-bridge diode imply that the diode voltage stress is low and the low-voltage drop diode can be utilized to further improve the efficiency.

4.4 Comparisons between the Proposed and Improved Converters

These two converters have many similarities, which are also their advantages, as follows.

1) With the parallel LLC resonant half-bridge configuration, zero-voltage switching of MOSFETs in the leading-leg can be ensured from true zero to full load, and thus, the super-junction MOSFET with slow reverse recovery body diode can be reliably used.

2) IGBTs in the lagging-leg work at zero-current switching with minimum circulating conduction loss because the parallel secondary-side DC voltage source effectively reset the circulating current, therefore, the turn-off loss and the conduction loss of the IGBTs are significantly reduced.
3) Duty cycle loss is negligible since the leakage inductance of the main transformer can be minimized without losing ZVS operation, thus, the current stresses through the primary-side semiconductors are minimized by the optimized turns ratio of the main transformer.

4) The topologies are suitable for wide-range output voltage or current source applications because of the buck-type configuration with the simple phase-shift pulse width modulation, and thus, they are a good candidate for the electrical vehicle battery charger. And this improved converter demonstrates better performances than the previous proposed one does.

a) Energy Transfer Method

These two converter topologies are repeated here in Fig.4.23 (a),(b).

![Fig. 4.23 Circuit configurations of the two converters](image)

(a)The converter proposed in CH3  (b) The improved converter in CH4

Fig. 4.23 Circuit configurations of the two converters

Fig.4.23 (a) shows that the output of LLC half bridge converter and the output of the phase shifted full bridge are in parallel to get the energy transferred. When it operates at $0 < t < D_{eff} \left( \frac{T_s}{2} \right)$, the phase shifted full bridge converter is in charge to transfer the energy to the load and no energy stored in $C_2$ or $C_1$ get transferred while the LLC converter charges the capacitors $C_1$ or $C_2$. Only when it operates at $D_{eff} \left( \frac{T_s}{2} \right) \leq t < 1$, the energy stored in $C_2$ or $C_1$ gets transferred to the load by the LLC converter. Thus when the effective duty cycle $D_{eff}$ approaches one, the energy stored in $C_2$ or $C_1$ has no chance to be transferred to the load.
Fig.23 (b) shows that the LLC half bridge converter and the phase shifted full bridge are in series to get the energy transferred. When it operates at $0 < t < D_{\text{eff}} \left( T_s / 2 \right)$, the phase shifted full bridge converter transfers the energy to the load and also energy stored in $C_2$ or $C_1$ get transferred to the load while the LLC converter charges the capacitors $C_1$ or $C_2$. When it operates at $D_{\text{eff}} \left( T_s / 2 \right) \leq t < 1$, the energy stored in $C_2$ or $C_1$ gets transferred to the load by the LLC converter. Thus whatever the effective duty cycle $D_{\text{eff}}$ is, the energy stored in $C_2$ or $C_1$ is always transferred to the load.

b) Transformer Size

The secondary rectifier voltage waveforms for these two converters are repeated here in Fig.4.24.

From Fig.4.24, it can be seen that the ratio of the main transformer in the improved converter can be $0.5 n_2$ smaller than that in the converter proposed in Chapter 3 under the same specifications due to the energy stored in $C_2$ or $C_1$ transferred to the load during the interval $0 < t < D_{\text{eff}} \left( T_s / 2 \right)$.

c) Output Inductor Size

![Fig. 4.25 Normalized peak-to-peak output inductor current vs. normalized output voltage](image)
Suppose \( n_1 \) is the same in the conventional full bridge, the proposed one in Chapter 3 and the improved one in this chapter, it can be seen from Fig.4.25 that the output inductor current ripple in the proposed converter can be reduced by \( \frac{n_2}{n_1} \) compared to the conventional full bridge, which means the inductance can be reduced by \( \frac{n_2}{n_1} \) compared to the conventional full bridge under the same current ripple condition, and the output inductor current ripple in the improved converter can be reduced by \( \frac{n_2}{2n_1-n_2} \) compared to the conventional full bridge, which means the inductance can be reduced by \( \frac{n_2}{2n_1-n_2} \) compared to the conventional full bridge under the same current ripple condition. Thus the inductance can be reduced by \( \frac{n_2(n_1-n_2)}{n_1(2n_1-n_2)} \) compared to the proposed converter. Since \( n_2<n_1 \), it can be seen that the improved converter has smallest current ripple.

4.5 Summary

To solve the problem at the certain case in the previous proposed novel hybrid resonant and PWM converter in chapter 3, an improved hybrid resonant and PWM converter has been proposed. Its basic operation has been analyzed and verified by simulations. Table 4.2 summarizes the performances of these four converters.

<table>
<thead>
<tr>
<th>Control method</th>
<th>ZVS range</th>
<th>Circulating current</th>
<th>Constant Current and Voltage</th>
<th>Output diode voltage stress</th>
</tr>
</thead>
<tbody>
<tr>
<td>PS FB</td>
<td>Fixed frequency</td>
<td>Limited range</td>
<td>High</td>
<td>Yes</td>
</tr>
<tr>
<td>LLC</td>
<td>Variable frequency</td>
<td>Full range</td>
<td>Low</td>
<td>No</td>
</tr>
<tr>
<td>Proposed converter</td>
<td>Fixed frequency</td>
<td>Full range</td>
<td>Low</td>
<td>Yes</td>
</tr>
<tr>
<td>Improved converter</td>
<td>Fixed frequency</td>
<td>Full range</td>
<td>Low</td>
<td>Yes</td>
</tr>
</tbody>
</table>

From Table 4.2 it can be seen that the improved hybrid converter can keep all the advantages of the previous proposed converter in chapter 3 repeated as follows:
1) With the parallel LLC resonant half-bridge configuration, zero-voltage switching of MOSFETs in the leading-leg can be ensured from true zero to full load, and thus, the super-junction MOSFET with slow reverse recovery body diode can be reliably used.

2) IGBTs in the lagging-leg work at zero-current switching with minimum circulating conduction loss because the parallel secondary-side DC voltage source effectively reset the circulating current, therefore, the turn-off loss and the conduction loss of the IGBTs are significantly reduced.

3) Duty cycle loss is negligible since the leakage inductance of the main transformer can be minimized without losing ZVS operation, thus, the current stresses through the primary-side semiconductors are minimized by the optimized turns ratio of the main transformer.

4) The topology is suitable for wide-range output voltage or current source applications because of the buck-type configuration with the simple phase-shift pulse width modulation, and thus, it is a good candidate for the electrical vehicle battery charger. And theoretically the improved converter demonstrates better performances than the previous proposed one does.

1) The auxiliary transformer is utilized fully since the LLC half bridge converter and the phase shifted full bridge are in series to get the energy transferred. When it operates at $0 < t < D_{\text{eff}} \left( \frac{T_s}{2} \right)$, the phase shifted full bridge converter transfers the energy to the load and also energy stored in $C_2$ or $C_1$ get transferred to the load while the LLC converter charges the capacitors $C_1$ or $C_2$. When it operates at $D_{\text{eff}} \left( \frac{T_s}{2} \right) \leq t < 1$, the energy stored in $C_2$ or $C_1$ gets transferred to the load by the LLC converter. Thus whatever the effective duty cycle $D_{\text{eff}}$ is, the energy stored in $C_2$ or $C_1$ is always transferred to the load.

2) The main transformer can be smaller. It is $0.5 n_2$ smaller than that in the converter proposed in Chapter 3 under the same specifications due to the energy stored in $C_2$ or $C_1$ transferred to the load during the interval $0 < t < D_{\text{eff}} \left( \frac{T_s}{2} \right)$.

3) The output inductor can be smaller than that in the proposed converter in chapter 3.
Conclusion

In this thesis, key features of different isolated DC-DC converters are discussed, and two new hybrid isolated converters are proposed for the EV battery charger application. The conventional isolated DC-DC converters suitable for high power applications are phase-shifted full-bridge and LLC converter. Although they are suitable for high efficiency, high power density and high reliability, they are also limited in some operating ranges. To make full use of their advantages and to avoid their drawbacks of losing zero-voltage switching and output regulation, a novel hybrid resonant and PWM converter combining resonant LLC half-bridge and phase shifted full-bridge topology is proposed for high efficiency and true full soft-switching range, which is very critical for the battery charger application because the battery requires a constant current charging with variable voltage and a constant voltage charging with variable current. A 3.4-kW hardware prototype has been designed, implemented and tested to verify that the proposed hybrid converter truly avoids the conventional converters while maintaining their advantages. In this proposed hybrid converter, the utilization efficiency of the auxiliary transformer is not that ideal. When the duty cycle is large, LLC converter charges one of the capacitors but the energy stored in the capacitor has no chance to be transferred to the output, resulting in the low utilization efficiency of the auxiliary transformer. To utilize the auxiliary transformer fully while keeping all the prominent features of the previous hybrid converter, an improved hybrid resonant and PWM converter is proposed, and its basic operation is analyzed and simulated to verify the validity.

These two proposed converters show some common advantages as described below.

1) With the parallel LLC resonant half-bridge configuration, zero-voltage switching of MOSFETs in the leading-leg can be ensured from true zero to full load, and thus, the super-junction MOSFET with slow reverse recovery body diode can be reliably used.

2) IGBTs in the lagging-leg work at zero-current switching with minimum circulating conduction loss because the parallel secondary-side DC voltage source effectively reset the circulating current, therefore, the turn-off loss and the conduction loss of the IGBTs are significantly reduced.
3) Duty cycle loss is negligible since the leakage inductance of the main transformer can be minimized without losing ZVS operation, thus, the current stresses through the primary-side semiconductors are minimized by the optimized turns ratio of the main transformer.

4) The topologies are suitable for wide-range output voltage or current source applications because of the buck-type configuration with the simple phase-shift pulse width modulation, and thus, they are a good candidate for the electrical vehicle battery charger.

The improved hybrid converter demonstrates some additional advantages:

1) The auxiliary transformer is utilized fully since the output of the LLC resonant converter is in series with the output load, thus the energy stored in the capacitor can be transferred to the output.

2) The main transformer can be smaller because the energy stored in the capacitor, which was charged by the LLC converter in the last effective duty cycle, can be transferred to the output during the effective duty cycle.

3) The output inductor of the improved hybrid converter can be smaller than that of the first proposed hybrid converter.
References


